TEXAS INSTRUMENTS

TPS25921A, TPS25921L

ZHCSCQ0 – AUGUST 2014

TPS25921x 具有精密限流和过压保护功能的 4.5V - 18V 熔丝

1 特性

- 4.5V - 18V 工作电压，最大绝对值 20V
- 90mΩ $R_{DS(ON)}$（典型值）
- 0.4A 至 1.6A 可调电流限值
- I_{LIMIT} 为 1A 且温度为 25°C 时限流精度达 ±2%
- ±3% 过压、欠压阈值
- 可编程的 dV_O/dt 控制
- 热关断故障输出、欠压闭锁 (UVLO) 和过压保护 (OVP)
- -40°C 至 125°C 的结温范围
- 自动重试和闭锁型号
- UL2367 认证正在处理中
- UL60950 - 单点故障测试期间安全

2 应用范围

- 大型家用电器，家用电器
- 机顶盒、数字化视频光盘 (DVD) 和游戏机
- 硬盘 (HDD) 和固态硬盘 (SSD)
- 智能仪表，气体分析仪
- 智能负载开关
- USB 开关
- 电源适配器器件

3 说明

TPS25921 是一款具有全套保护功能的紧凑型多功能熔丝。 它具有较宽的工作电压，可实现对多种常用直流 (DC) 总线的控制。 室温下限流精度达 ±2%，这种优异的精度使得 TPS25921 成为多种系统保护应用的理想选择。

而且它还具有过流保护、过压保护和欠压保护等多种可编程功能，能够对负载、电源和器件提供保护。欠压和过压条件下的阈值精度为 3%，无需监控电路即可确保对总线电压进行严密控制。 此外，还针对系统状态监视和下游负载控制提供了故障标志输出 $\overline{(FLT)}$。

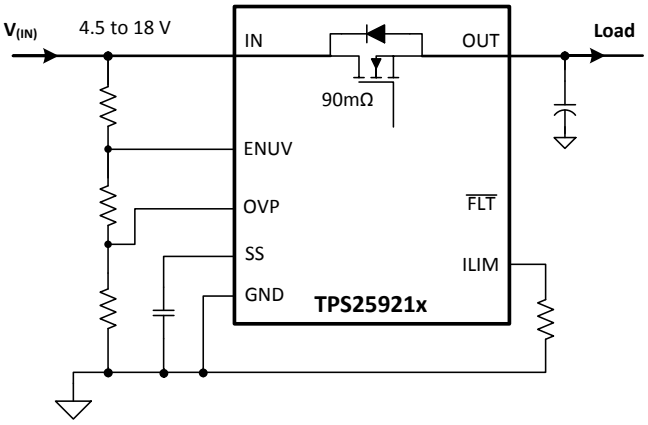
对于热插拔电路板，TPS25921 提供了浪涌电流控制和可编程的输出斜坡速率。 为实现设计灵活性的最大化，可使用软启动 (SS) 引脚处的电容器编程设定输出斜坡速率。

器件信息(1)

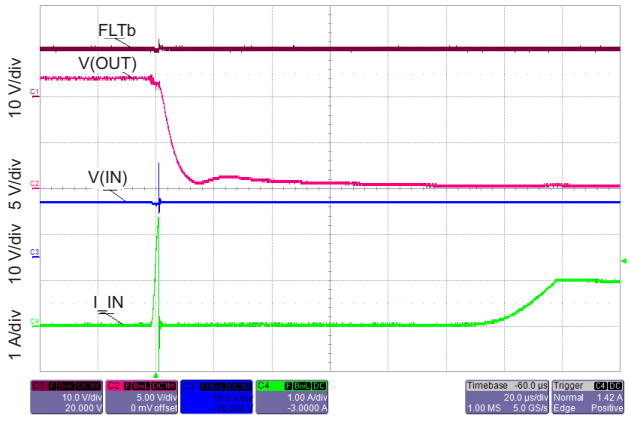
部件号	封装	封装尺寸（标称值）
TPS25921A	SOIC	4.90mm x 3.91mm
TPS25921L		

(1) 如需了解所有可用封装，请见数据表末尾的可订购产品附录。

4 应用电路原理图



12V 短路响应



PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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5 修订历史记录

日期	修订版本	注释
2014 年 8 月	*	最初发布。

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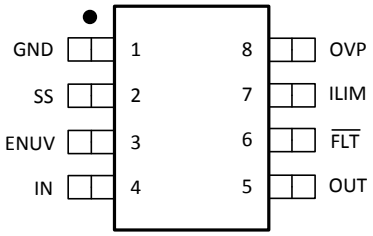
6 Pin Configuration and Functions

SOIC (D) 8 PIN PACKAGE
(TOP VIEW)



Pin Functions

NAME	NUMBER	DESCRIPTION
GND	1	Ground.
SS	2	A capacitor from this pin to GND sets the ramp rate of output voltage at device turn-on.
ENUV	3	Input for setting programmable undervoltage lockout threshold. An undervoltage event will open internal FET and assert $\overline{FLT}$ to indicate power-failure. When pulled to GND, resets the thermal fault latch in TPS25921L.
IN	4	Power Input and supply voltage of the device.
OUT	5	Power Output of the device.
$\overline{FLT}$	6	Fault event indicator, goes low to indicate fault condition due to Undervoltage, Overvoltage, and Thermal shutdown event. A nuisance fast trip does not trigger fault. It is an open drain output.
ILIM	7	A resistor from this pin to GND will set the overload and short circuit limit.
OVP	8	Input for setting programmable overvoltage protection threshold. An overvoltage event will open the internal FET and assert $\overline{FLT}$ to indicate overvoltage.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		VALUE(2)		UNIT
		MIN	MAX	
Input voltage range	IN, OUT, ENUV, OVP, $\overline{FLT}$	–0.3	20	V
	IN (10 ms Transient)		22	
	ILIM, SS	–0.3	7	
Sink current	SS		5	mA
	$\overline{FLT}$		100	mA
Source current	ILIM, SS, $\overline{FLT}$	Internally Limited		
Maximum junction temperature, T_J		Internally Limited		°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential voltages, are with respect to network ground terminal.

7.2 Handling Ratings

			MIN	MAX	UNIT
T_{stg}	Storage temperature range		-65	150	°C
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	–2	2	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	–0.5	0.5	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP	MAX	UNIT
Input voltage range	IN	4.5		18	V
	OUT, OVP, ENUV, $\overline{FLT}$	0		18	
	SS	0		6	
	ILIM	0		3.3	
Resistance	ILIM	35.7	95.3	158	kΩ
External capacitance	OUT	0.1	1		µF
	SS		1	1000	nF
Operating junction temperature range, T_J		–40	25	125	°C

7.4 Thermal Characteristics(1)

THERMAL METRIC		TPS2592xx	UNIT
		SOIC (8) PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	120.8	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	65.5	
$R_{\theta JB}$	Junction-to-board thermal resistance	51.8	
ψ_{JT}	Junction-to-top characterization parameter	17.4	
ψ_{JB}	Junction-to-board characterization parameter	61.2	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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7.5 Electrical Characteristics

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, 4.5 V ≤ $V_{(IN)}$ ≤ 18 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages are referenced to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY VOLTAGE AND INTERNAL UNDERVOLTAGE LOCKOUT						
$V_{(IN)}$	Operating Input Voltage		4.5		18	V
$V_{(UVR)}$	UVLO Threshold, Rising		4.10	4.26	4.40	V
$V_{(UVHys)}$	UVLO Hysteresis		168	224	279	mV
$I_{Q(\ ON)}$	Supply Current, Enabled	$V_{(ENUV)}$ = 2 V, $V_{(IN)}$ = 12 V	0.22	0.41	0.58	mA
$I_{Q(\ OFF)}$	Supply Current, Disabled	$V_{(ENUV)}$ = 0 V, $V_{(IN)}$ = 12 V	0.08	0.132	0.20	mA
OVERVOLTAGE PROTECTION (OVP) INPUT						
$V_{(OVPR)}$	Overvoltage Threshold Voltage, Rising		1.35	1.39	1.43	V
$V_{(OVPF)}$	Overvoltage Threshold Voltage, Falling		1.30	1.34	1.37	V
$I_{(OVP)}$	OVP Input Leakage Current	0V ≤ $V_{(OVP)}$ ≤ 18 V	–100	0	100	nA
ENABLE AND UNDERVOLTAGE LOCKOUT (ENUV) INPUT						
$V_{(ENR)}$	ENUV Threshold voltage, rising		1.36	1.39	1.42	V
$V_{(ENF)}$	ENUV Threshold voltage, falling		1.30	1.34	1.37	V
$V_{(ENF_RST)}$	ENUV Threshold voltage to reset thermal fault, falling		0.5	0.61	0.8	V
I_{EN}	EN Input leakage current	0 ≤ $V_{(ENUV)}$ ≤ 18 V	–100	0	100	nA
SOFT START: OUTPUT RAMP CONTROL (SS)						
$I_{(SS)}$	SS charging current	$V_{(SS)}$ = 0 V	0.9	1.04	1.2	µA
$R_{(SS)}$	SS discharging resistance	$V_{(ENUV)}$ = 0 V, $I_{(SS)}$ = 10 mA sinking	60	70	85	Ω
$V_{(SSmax)}$	SS maximum capacitor voltage			5.5		V
$GAIN_{(SS)}$	SS to OUT gain	$\Delta V_{(OUT)}/\Delta V_{(SS)}$	4.81	4.86	4.92	V/V
CURRENT LIMIT PROGRAMMING (ILIM)						
$I_{(ILIM)}$	ILIM Bias current		6	10	16	µA
I_{LIMIT}	Current Limit(1)	$R_{(ILIM)}$ = 35.7 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 1 V	0.284	0.368	0.452	A
		$R_{(ILIM)}$ = 45.3 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 1 V	0.394	0.471	0.547	
		$R_{(ILIM)}$ = 95.3 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 1 V, T_A = T_J= 25°C	0.98	1.0	1.02	
		$R_{(ILIM)}$ = 95.3 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 1 V	0.93	1.0	1.062	
		$R_{(ILIM)}$ = 150 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 1 V	1.43	1.57	1.7	
		$R_{(ILIM)}$ = SHORT, Shorted resistor current limit $R_{(ILIM)}$ = OPEN, Open resistor current limit (Single Point Failure Test: UL60950)	0.12	0.257	0.406	
I_{OS}	Short-circuit current limit(1)	$R_{(ILIM)}$ = 35.7 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 12 V	0.275	0.356	0.438	A
		$R_{(ILIM)}$ = 45.3 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 12 V	0.376	0.45	0.522	
		$R_{(ILIM)}$ = 95.3 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 12 V	0.837	0.9	0.964	
		$R_{(ILIM)}$ = 150 kΩ, ($V_{(IN)}$ - $V_{(OUT)}$) = 12 V	1.219	1.34	1.46	
$I_{(FASTRIP)}$	Fast-Trip comparator threshold	$R_{(ILIM)}$ in kΩ		0.0142 x $R_{(ILIM)}$ + 0.36		A
$V_{(ILIMopen)}$	ILIM Open resistor detect threshold	$V_{(ILIM)}$ Rising, $R_{(ILIM)}$ = OPEN	2.81	3.0	3.25	V
MOSFET – POWER SWITCH						
$R_{DS(on)}$	FET ON resistance(2)	–40°C ≤ T_J ≤ 85°C	55	87	120	mΩ
		–40°C ≤ T_J ≤ 125°C	55	87	135	
PASS FET OUTPUT (OUT)						
$I_{lkg(OUT)}$	OUT Bias current in off state	$V_{(ENUV)}$ = 0 V, $V_{(OUT)}$ = 0 V (Sourcing)	–2	0	1	µA
$I_{sink(OUT)}$		$V_{(ENUV)}$ = 0V, $V_{(OUT)}$ = 300 mV (Sinking)	5	7	10	

(1) Pulse-testing techniques maintain junction temperature close to ambient temperature. Thermal effects must be taken into account separately.
(2) The limits for these parameters are specified based on design and characterization data, and are not tested during production.

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Electrical Characteristics (continued)

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, 4.5 V ≤ $V_{(IN)}$ ≤ 18 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages are referenced to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
FAULT FLAG ($\overline{FLT}$): ACTIVE LOW						
$R_{(\overline{FLT})}$	$\overline{FLT}$ Pull down Resistance	Device in fault condition, $V_{(ENUV)}$ = 0V, $I_{(\overline{FLT})}$ = 100mA	22	26	32	Ω
$I_{(\overline{FLT})}$	$\overline{FLT}$ Input Leakage Current	Device not in fault condition, $V_{(\overline{FLT})}$ = 0V, 18V	–0.5	0	0.5	µA
THERMAL SHUT DOWN (TSD)						
$T_{(TSD)}$	TSD Threshold, rising(3)			155		°C
$T_{(TSDhys)}$	TSD Hysteresis(3)			20		°C
	Thermal fault: Latched or Auto Retry	TPS25921L		LATCHED		
		TPS25921A		AUTO-RETRY		

(3) The limits for these parameters are specified based on design and characterization data, and are not tested during production.

7.6 Timing Requirements

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, $V_{(IN)}$= 12 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages are referenced to GND (unless otherwise noted). Refer to Figure 26 for the timing diagrams

			MIN	TYP	MAX	UNIT
ENABLE AND UNDERVOLTAGE LOCKOUT (ENUV) INPUT						
$t_{OFF(dly)}$	Turn Off delay	ENUV ↓ to $V_{(OUT)}$↓		8		µs
$t_{ON(dly)}$	Turn-On delay	ENUV ↑ to $V_{(OUT)}$ = 1V, $C_{(SS)}$ = OPEN		96		µs
		ENUV ↑ to $V_{(OUT)}$ = 1V, $C_{(SS)}$ > 0.39nF, [C(dVdT) in nF]		14.5 + 0.5 x (70p + $C_{(SS)}$)		
OVERVOLTAGE PROTECTION (OVP) INPUT						
$t_{OVP(dly)}$	OVP Disable delay	OVP↑ to $V_{(OUT)}$↓		8		µs
SOFT START: OUTPUT RAMP CONTROL (SS)						
t_{SS}	Output ramp time	ENUV ↑ to $V_{(OUT)}$ = 11.7 V, with $C_{(SS)}$ = open , $C_{(OUT)}$ = 2.2 µF	0.2	0.26	0.33	ms
		ENUV ↑ to $V_{(OUT)}$ = 11.7 V, with $C_{(SS)}$ = 1 nF, $C_{(OUT)}$ = 2.2 µF	2.1	3	3.6	
CURRENT LIMIT PROGRAMMING (ILIM)						
$t_{FASTRIP(dly)}$	Fast-Trip comparator delay	$I_{(OUT)}$ > $I_{(FASTRIP)}$		3		µs
THERMAL SHUT DOWN (TSD)						
$t_{TSD(dly)}$	Retry Delay after TSD recovery, T_J < [$T_{(TSD)}$ - 20°C]	TPS25921A Only, $V_{(IN)}$ = 12 V		150		ms
		TPS25921A Only, $V_{(IN)}$ = 4.5 V		100		ms

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7.7 Typical Characteristics

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, $V_{(IN)}$= 12 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, $C_{(OUT)}$ = 2.2 µF, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages referenced to GND (unless otherwise noted). For all oscilloscope waveforms T_A = 25°C.

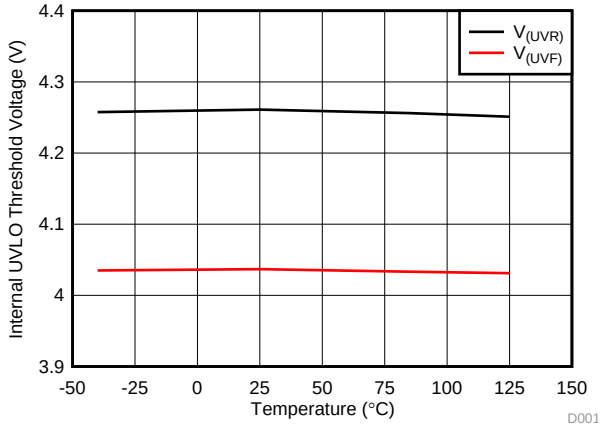


Figure 1. UVLO Threshold Voltage vs Temperature

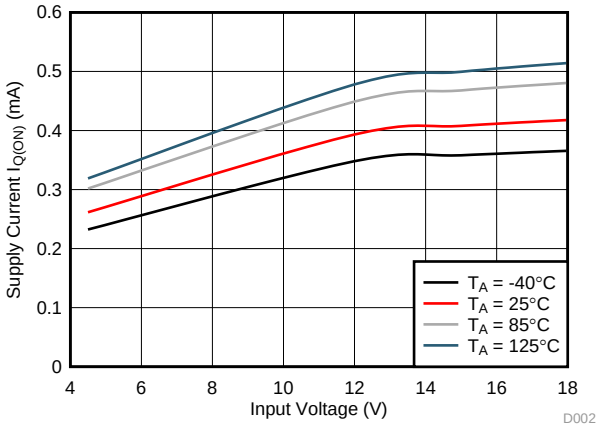


Figure 2. Input Supply Current vs Supply Voltage During Normal Operation

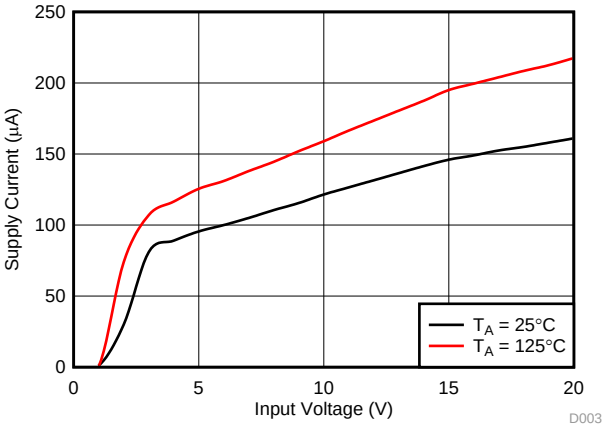


Figure 3. Input Supply Current vs Supply Voltage at Shutdown

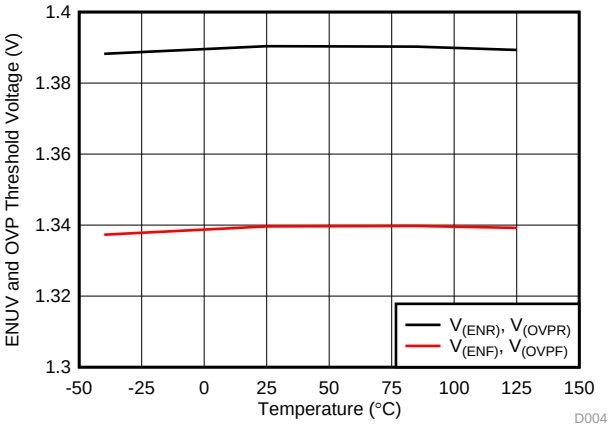


Figure 4. ENUV and OVP Threshold Voltage vs Temperature

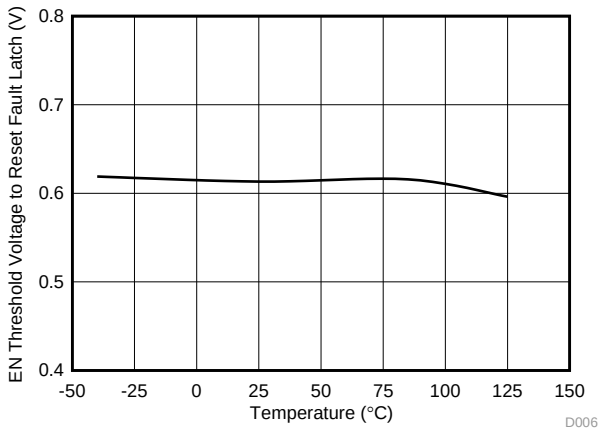


Figure 5. EN Threshold Voltage to Reset Fault Latch vs Temperature

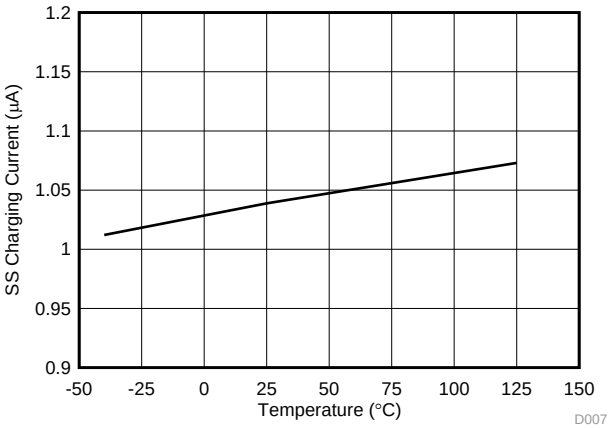


Figure 6. SS Pin Charging Current vs Temperature

Typical Characteristics (continued)

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, $V_{(IN)}$= 12 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, $C_{(OUT)}$ = 2.2 µF, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages referenced to GND (unless otherwise noted). For all oscilloscope waveforms T_A = 25°C.

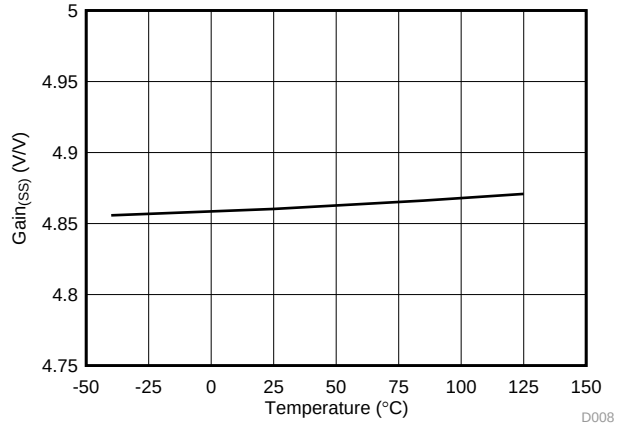


Figure 7. $GAIN_{(SS)}$ vs Temperature

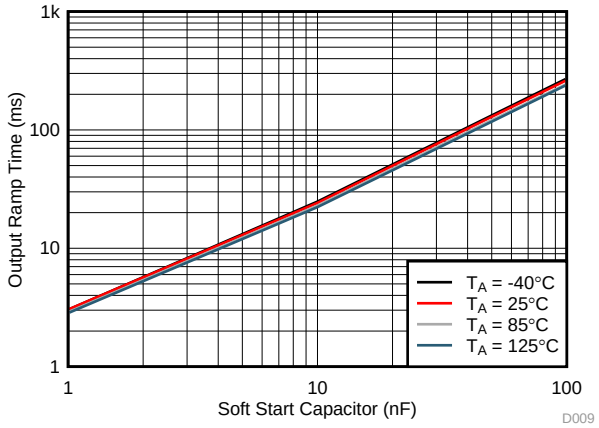
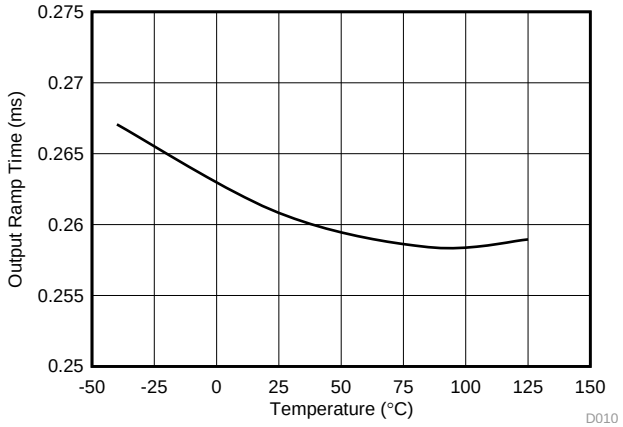


Figure 8. Output Ramp Time vs $C_{(SS)}$



$C_{(SS)}$ = Open

Figure 9. Output Ramp Time vs Temperature

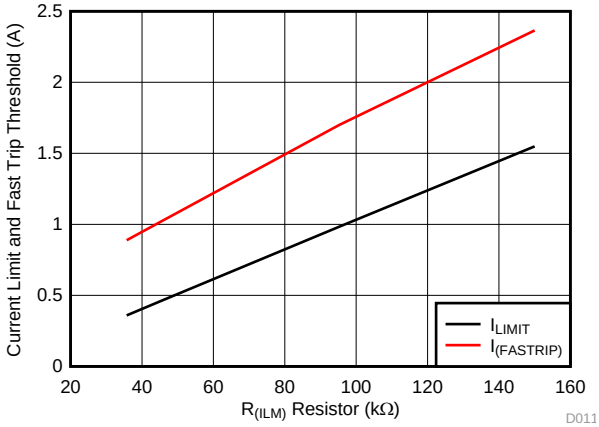


Figure 10. Current Limit vs Current Limit Resistor

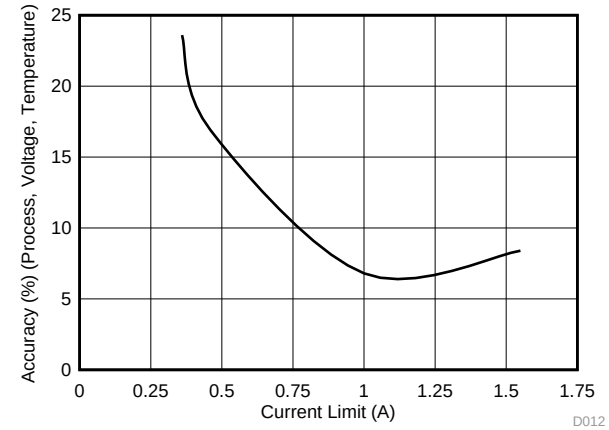


Figure 11. Current Limit Accuracy vs Current Limit

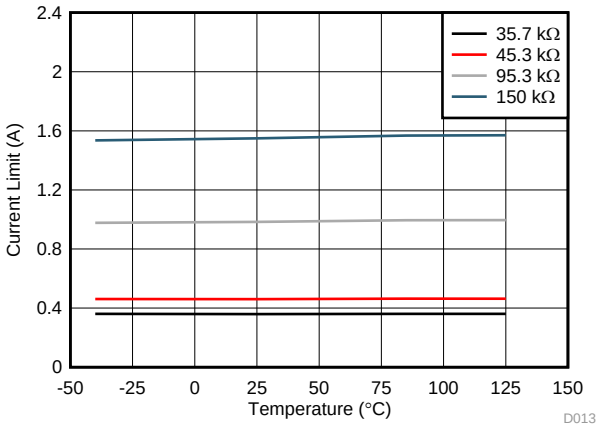


Figure 12. Current Limit vs Temperature Across $R_{(ILIM)}$

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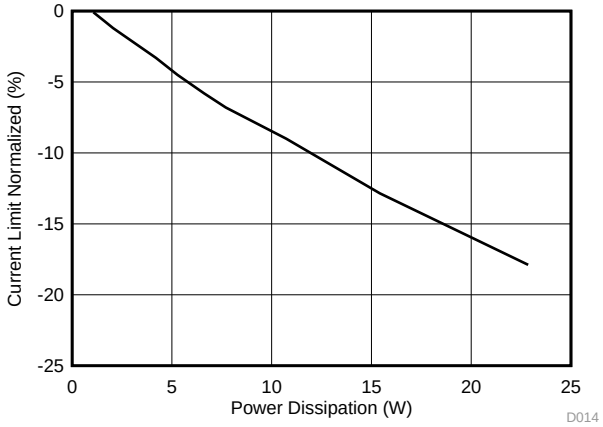
Typical Characteristics (continued)

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, $V_{(IN)}$= 12 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, $C_{(OUT)}$ = 2.2 µF, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages referenced to GND (unless otherwise noted). For all oscilloscope waveforms T_A = 25°C.



$P_D = [V_{(IN)} - V_{(OUT)}]*I_{LIMIT}$

Figure 13. Current Limit Normalized (%) vs Power Dissipation in the Device P_D

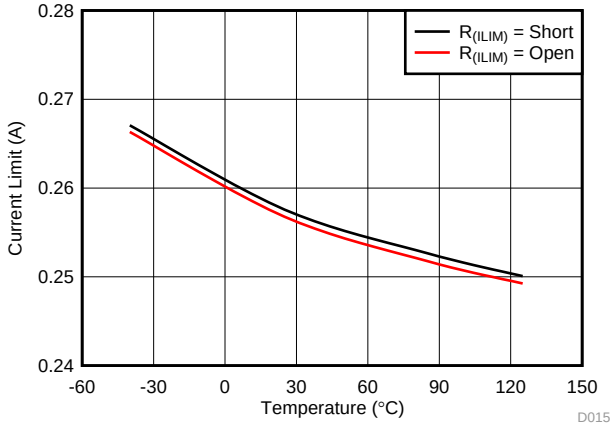


Figure 14. Current Limit for $R_{(ILIM)}$ = Open and Short vs Temperature

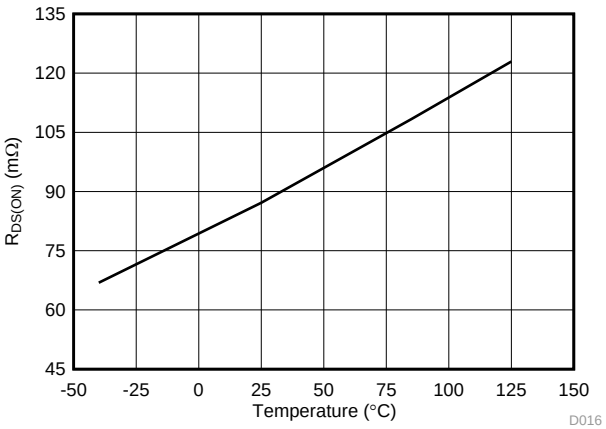
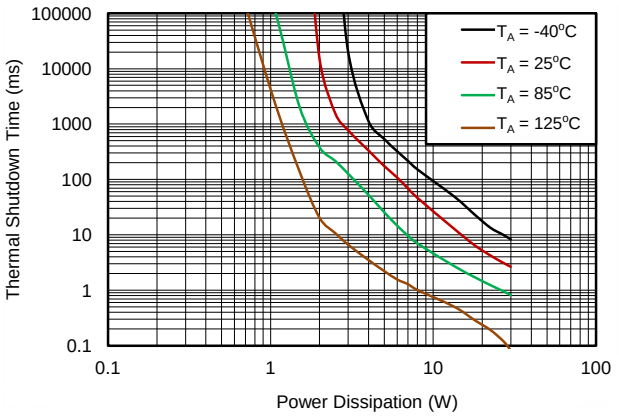
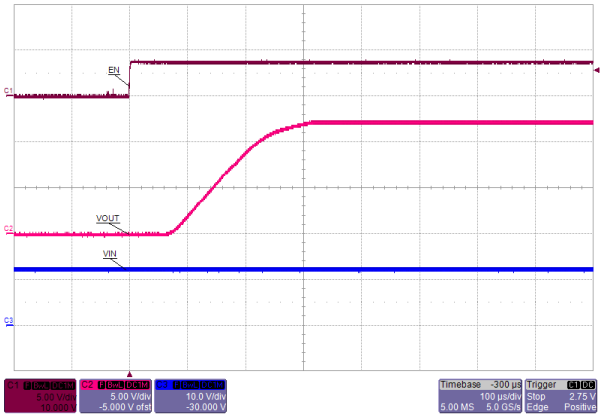


Figure 15. $R_{DS(ON)}$ vs Temperature



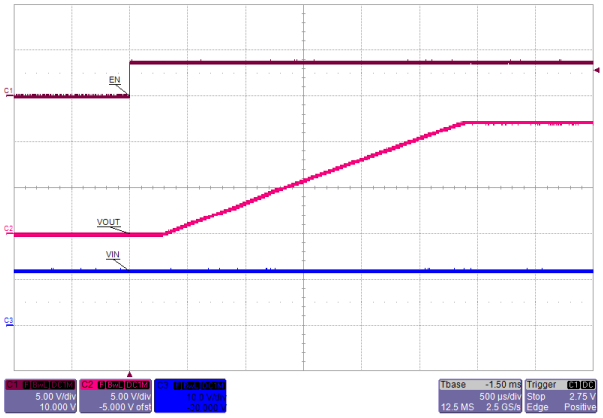
Taken on 1-Layer board, 2oz.(0.08-mm thick) with GND plane area: 14 cm2 (bottom)

Figure 16. Thermal Shutdown Time vs Power Dissipation



$C_{(SS)}$ = Open $C_{(OUT)}$ = 4.7 nF

Figure 17. Turn ON with Enable



$C_{(SS)}$ = 1nF $C_{(OUT)}$ = 4.7 nF

Figure 18. Turn ON with Enable

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Typical Characteristics (continued)

Conditions (unless otherwise noted) are –40°C ≤ T_J ≤ 125°C, $V_{(IN)}$= 12 V, $V_{(EN\ UV)}$ = 2 V, $V_{(OVP)}$ = 0 V, $R_{(ILIM)}$ = 95.3 kΩ, $C_{(OUT)}$ = 2.2 µF, C_{SS} = OPEN, FLT = OPEN. Positive current into terminals. All voltages referenced to GND (unless otherwise noted). For all oscilloscope waveforms T_A = 25°C.

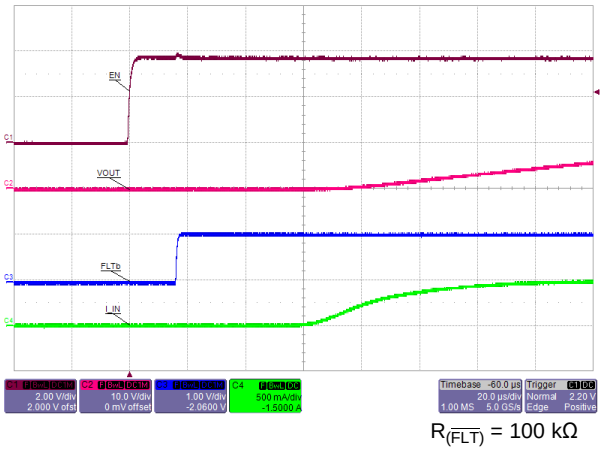

Figure 19. EN Turn ON Delay : EN ↑ to Output Ramp ↑

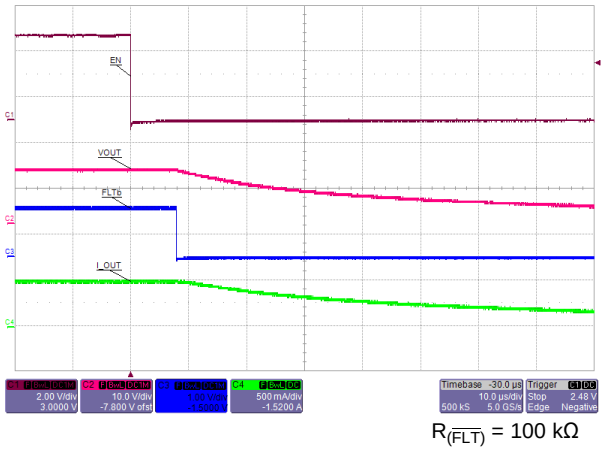

Figure 20. EN Turn OFF Delay : EN ↓ to Fault ↓

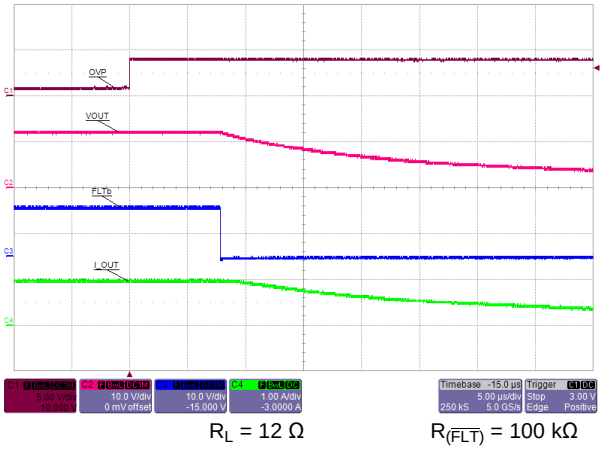

Figure 21. OVP Turn OFF delay: OVP ↑ to Fault ↓

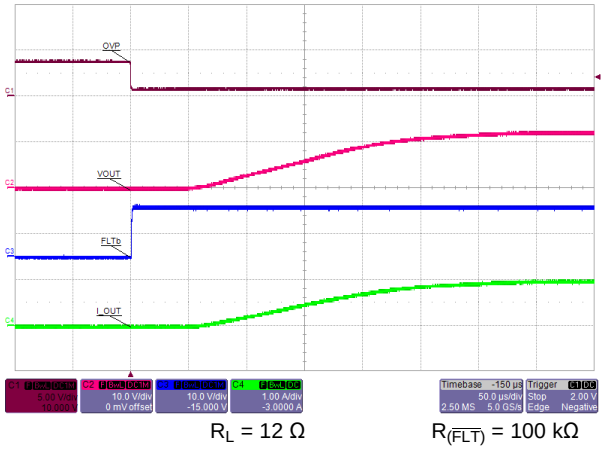

Figure 22. OVP Turn ON delay: OVP ↓ to Output Ramp ↑

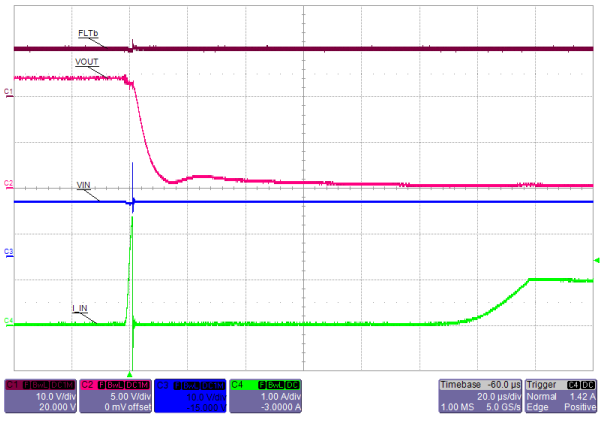

Figure 23. Hot-Short: Fast Trip Response and Current Regulation

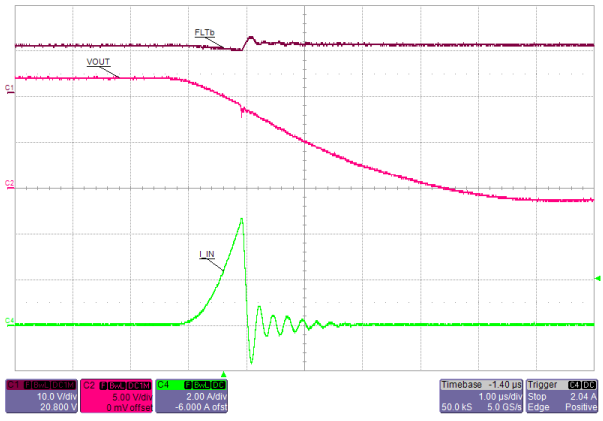

Figure 24. Hot-Short: Fast Trip Response (Zoomed)

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8 Parametric Measurement Information

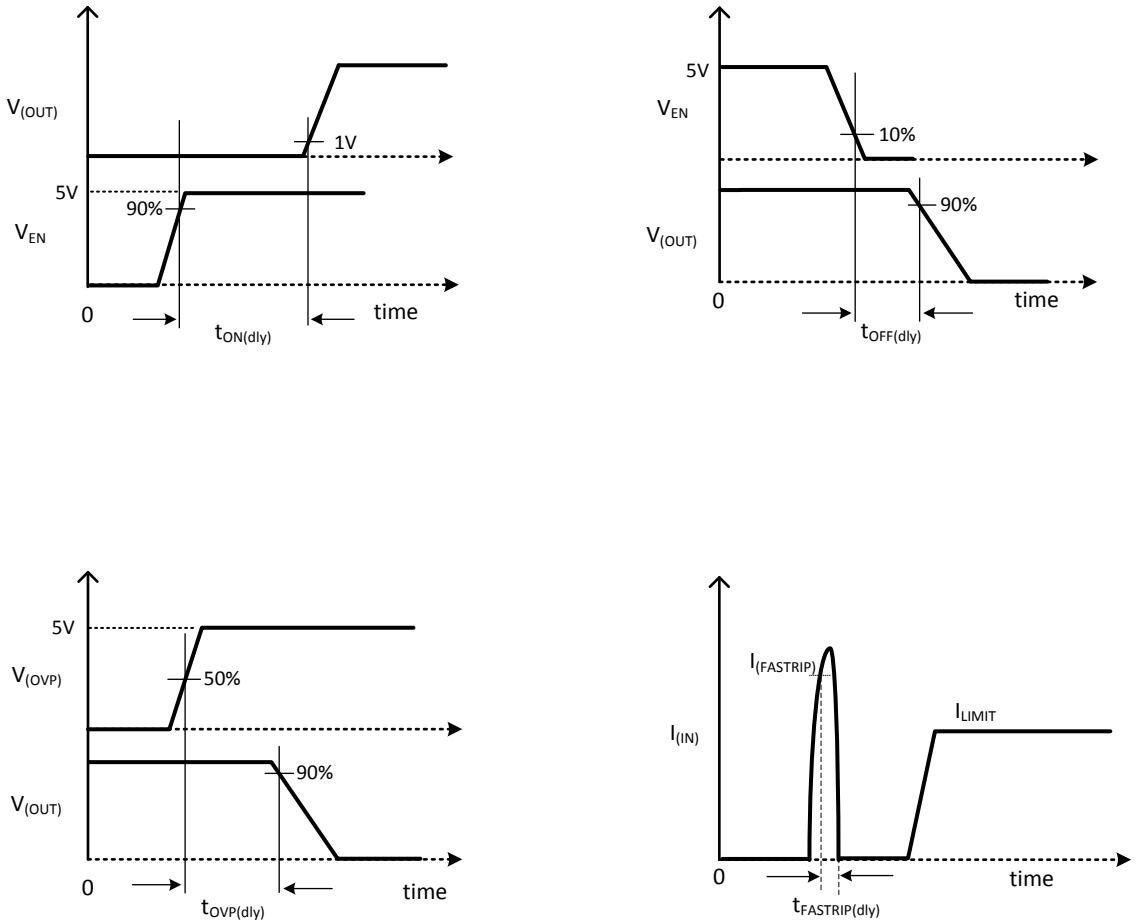

Figure 25. Timing Diagrams

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9 Detailed Description

9.1 Overview

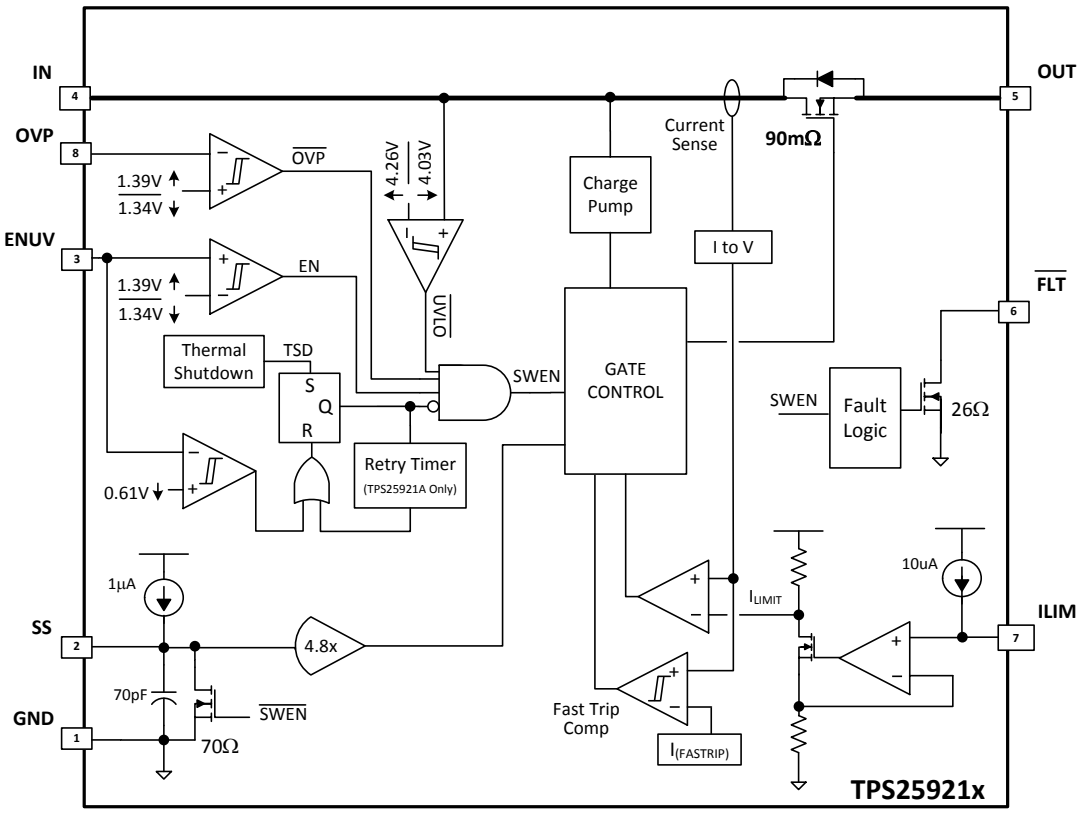
TPS25921 is a smart eFuse with enhanced built-in protection circuitry. It provides robust protection for all systems and applications powered from 4.5 V to 18 V.

For hot-plug-in boards, the device provides in-rush current control and programmable output ramp-rate. TPS25921 integrates overcurrent and short circuit protection. The precision overcurrent limit helps to minimize over design of the input power supply, while the fast response short circuit protection immediately isolates the load from input when a short circuit is detected. The device allows the user to program the overcurrent limit threshold between 0.4 A and 1.6 A via an external resistor. The device provides precise monitoring of voltage bus for brown-out and overvoltage conditions and asserts fault for downstream system. Its threshold accuracy of 3% ensures tight supervision of bus, eliminating the need for a separate supply voltage supervisor chip. TPS25921 is designed to protect systems such as White Goods, STBs, DTVs, Smart Meters and Gas Analyzers.

The additional features include:

- Over temperature protection to safely shutdown in the event of an overcurrent event
- Fault reporting for brown-out and overvoltage faults
- A choice of latched or automatic restart mode

9.2 Functional Block Diagram



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9.3 Feature Description

9.3.1 Enable and Adjusting Undervoltage Lockout (UVLO)

The ENUV pin controls the ON/OFF state of the internal FET. A voltage $V_{(ENUV)} < V_{(ENF)}$ on this pin turns off the internal FET, thus disconnecting IN from OUT.

Toggling the ENUV pin below $V_{(ENF_RST)}$ resets the TPS25921L that has latched off due to a fault condition. The internal de-glitch delay on ENUV falling edge is kept low for quick detection of power failure. For applications where a higher de-glitch delay on ENUV is desired, or when the supply is particularly noisy, it is recommended to use an external filter capacitor from the ENUV terminal to GND.

The undervoltage lockout threshold can be programmed by using an external resistor divider from the supply IN terminal to the ENUV terminal to GND as shown in Figure 26. When an undervoltage or input power fail event is detected, the internal FET is quickly turned off, and $\overline{FLT}$ is asserted. If the undervoltage lockout function is not needed, the ENUV pin should be connected to the IN terminal. The ENUV terminal should not be left floating.

TPS25921 also implements internal undervoltage lockout (UVLO) circuitry on the IN pin. The device gets disabled when the IN terminal voltage falls below internal UVLO Threshold $V_{(UVF)}$.

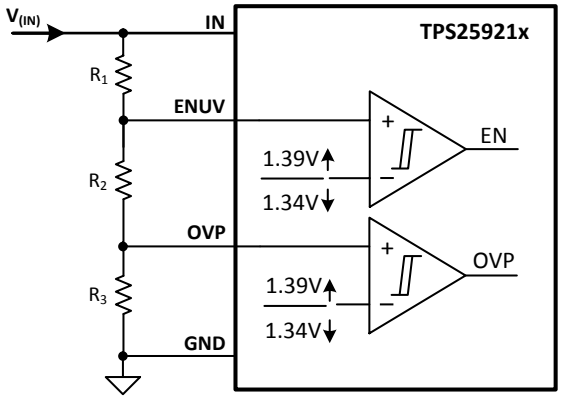

Figure 26. UVLO and OVP Thresholds Set By R_1, R_2 and R_3

9.3.2 Overvoltage Protection (OVP)

TPS25921 incorporates circuits to protect the system during overvoltage conditions. A resistor divider, connected from the supply to OVP terminal to GND (as shown in Figure 26), programs the overvoltage threshold. A voltage more than $V_{(OVPR)}$ on the OVP pin turns off the internal FET and protects the downstream load. This pin should be tied to GND when not used.

9.3.3 Hot Plug-in and In-Rush Current Control

TPS25921 is designed to control the in-rush current upon insertion of a card into a live backplane or other "hot" power source. This limits the voltage sag on the backplane's supply voltage and prevents unintended resets of the system power. A slew rate controlled startup (SS) also helps to eliminate conductive and radiated interference. An external capacitor from the SS pin to GND defines the slew rate of the output voltage at power-on (as shown in Figure 27). The equation governing slew rate at start-up is shown in Equation 1 :

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Feature Description (continued)

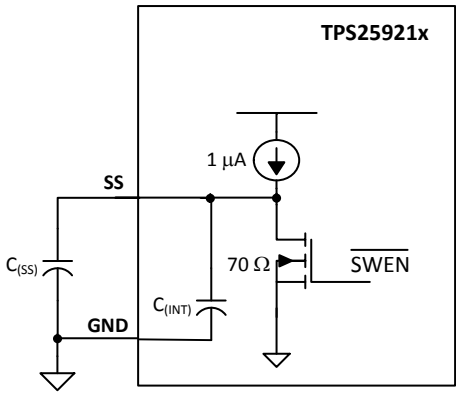

Figure 27. Output Ramp Up Time t_{dVdT} is Set by $C_{(dVdT)}$

$$I_{(SS)} = \frac{(C_{(SS)} + C_{(INT)})}{Gain_{(SS)}} \times \frac{dV_{(OUT)}}{dt} \quad (1)$$

Where:

- $I_{(SS)}$ = 1 µA (typical)
- $\frac{dV_{(OUT)}}{dt}$ = Desired output slew rate
- $GAIN_{(SS)} = \Delta V_{(OUT)}/\Delta V_{(SS)}$ gain = 4.85

The total ramp time (t_{SS}) of $V_{(OUT)}$ for 0 to $V_{(IN)}$ can be calculated using Equation 2:

$$t_{SS} = 20.6 \times 10^{4} \times V_{(IN)} \times \left(C_{(SS)} + 0.07\right) \quad (2)$$

The inrush current, $I_{(INRUSH)}$ can be calculated as

$$I_{(INRUSH)} = C_{(OUT)} \times \frac{V_{(IN)}}{t_{SS}} \quad (3)$$

The SS pin can be left floating to obtain a predetermined slew rate (t_{SS}) on the output. When terminal is left floating, the device sets an internal ramp rate of ~50V/ms for output ($V_{(OUT)}$) ramp.

Figure 36 and Figure 37 illustrate the inrush current control behavior of the device. For systems where load is present during start-up, the current never exceeds the overcurrent limit set by $R_{(ILIM)}$ resistor for the application. For defining appropriate charging time/rate under different load conditions, refer to the *Setting Output Voltage Ramp time (t_{SS})* section.

9.3.4 Overload and Short Circuit Protection :

At all times load current is monitored by sensing voltage across an internal sense resistor. During overload events, current is limited to the current limit (I_{LIMIT}) programmed by $R_{(ILIM)}$ resistor

$$I_{LIMIT} = 10.73 \times 10^{-3} \times R_{(ILIM)} - 0.018 \quad (4)$$

$$R_{(ILIM)} = \frac{I_{LIMIT} + 0.018}{10.73 \times 10^{-3}} \quad (5)$$

- I_{LIMIT} is overload current limit in Ampere
- $R_{(ILIM)}$ is the current limit programming resistor in kΩ

TPS25921 incorporates two distinct overcurrent protection levels: the current limit (I_{LIMIT}) and the fast-trip threshold ($I_{(FASTRIP)}$). The fast trip and current limit operations are shown in Figure 28.

Bias current on ILIM pin directly controls current-limiting behavior of the device, and PCB routing of this node must be kept away from any noisy (switching) signals.

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Feature Description (continued)

9.3.4.1 Overload Protection

For overload conditions, the internal current-limit amplifier regulates the output current to I_{LIMIT}. The output voltage droops during current limit regulation, resulting in increased power dissipation in the device. If the device junction temperature reaches the thermal shutdown threshold ($T_{(TSD)}$), the internal FET is turned off. Once in thermal shutdown, The TPS25921L version stays latched off, whereas TPS25921A commences an auto-retry cycle $t_{TSD(dly)}$ ms after $T_J < [T_{(TSD)} - 20°C]$. During thermal shutdown, the fault pin $\overline{FLT}$ pulls low to signal a fault condition. Figure 40 and Figure 41 illustrate overload behavior.

9.3.4.2 Short Circuit Protection

During a transient short circuit event, the current through the device increases very rapidly. As current-limit amplifier cannot respond quickly to this event due to its limited bandwidth, the device incorporates a fast-trip comparator, with a threshold $I_{(FASTRIP)}$. When the current through the internal FET exceeds $I_{(FASTRIP)}$ ($I_{(OUT)} > I_{(FASTRIP)}$), this comparator shuts down the pass device within 3 µs and terminates the rapid short-circuit peak current. The $I_{(FASTRIP)}$ threshold is dependent on programmed overload current limit and function of $R_{(ILIM)}$. See Equation 6 for the calculation.

$$I_{(FASTRIP)} = 1.42 \times 10^{-2} \times R_{(ILIM)} + 0.36 \quad (6)$$

where

- $I_{(FASTRIP)}$ is fast trip current limit in Ampere
- $R_{(ILIM)}$ is the current limit resistor in kΩ

The fast-trip circuit holds the internal FET off for only a few microseconds, after which the device attempts to turn back on normally, allowing the current-limit loop to regulate the output current to I_{LIMIT}. Then, device behaves similar to overload condition. Figure 42 through Figure 44 illustrate the behavior of the system when the current exceeds the fast-trip threshold.

9.3.4.3 Start-Up with Short on Output

During start-up into a short circuit current is limited to I_{LIMIT}. Figure 45 and Figure 46 illustrate start-up with a short on the output. This feature helps in quick fault isolation and hence ensures stability of the DC bus.

9.3.4.4 Constant Current Limit Behavior during Overcurrent Faults

When power dissipation in the internal FET [$P_D = (V_{(IN)} - V_{(OUT)}) \times I_{(OUT)}$] > 2 W, there is a ~1 to 20 % thermal fold back in the current limit value so that the regulated current drops from I_{LIMIT} to I_{OS}. Eventually, the device shuts down due to over temperature.

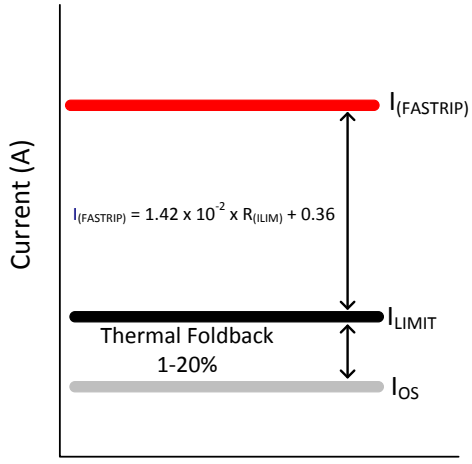

Figure 28. Overcurrent Protection Levels

Feature Description (continued)

9.3.5 FAULT Response

The $\overline{FLT}$ open-drain output is asserted (active low) during undervoltage, overvoltage and thermal shutdown conditions. The $\overline{FLT}$ signal remains asserted until the fault condition is removed and the device resumes normal operation. During thermal shutdown, TPS25921L version stays latched off, whereas TPS25921A commences an auto-retry cycle $t_{TSD(dly)}$ millisecond after $T_J < [T_{(TSD)} - 20°C]$. For TPS25921L, thermal fault latch can be reset by cycling the ENUV pin below $V_{(ENF_RST)}$ threshold. A nuisance fast trip does not trigger fault.

Connect $\overline{FLT}$ with a pull up resistor to Input or Output voltage rail. $\overline{FLT}$ may be left open or tied to ground when not used.

9.3.6 IN, OUT and GND Pins

The IN pin should be connected to the power source. A ceramic bypass capacitor close to the device from IN to GND is recommended to alleviate bus transients. The recommended operating voltage range is 4.5 V – 18 V.

The OUT pin should be connected to the load. $V_{(OUT)}$ in the ON condition, is calculated using the Equation 7

$$V_{(OUT)} = V_{(IN)} - \left(R_{DS(ON)} \times I_{(OUT)}\right) \quad (7)$$

where, $R_{DS(ON)}$ is the ON resistance of the internal FET.

GND terminal is the most negative voltage in the circuit and is used as a reference for all voltage reference unless otherwise specified.

9.3.7 Thermal Shutdown:

Internal over temperature shutdown disables/turns off the FET when $T_J > 155°C$ (typical). The TPS25921L version latches off the internal FET, whereas TPS25921A commences an auto-retry cycle $t_{TSD(dly)}$ milliseconds after T_J drops below $[T_{(TSD)} - 20°C]$. During the thermal shutdown, the fault pin $\overline{FLT}$ is pulled low to signal a fault condition.

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9.4 Device Functional Modes

9.4.1 Shutdown Control

The internal FET and hence the load current can be remotely switched off by taking the ENUV pin below its 1.34 V threshold with an open collector or open drain device as shown in Figure 29. Upon releasing the ENUV pin the device turns on with soft-start cycle.

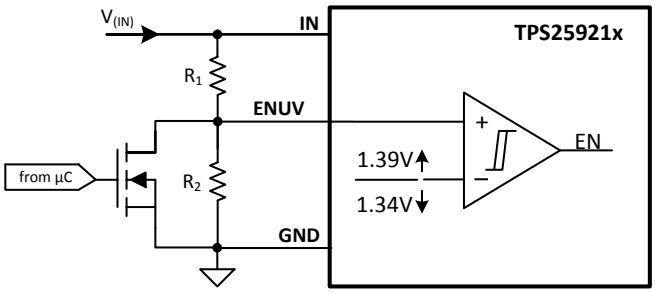

Figure 29. Shutdown Control

9.4.2 Operational Overview of Device Functions

The Table 1 below elucidates the device functionality for various conditions

Table 1. Operational Overview of Device Functions

Device	TPS25921
Start Up	Inrush ramp controlled by capacitor at SS pin
	Inrush limited to I_{LIMIT} level as set by $R_{(ILIM)}$
	If $T_J > T_{(TSD)}$ device shuts off
Overcurrent Response	Current is limited to $I_{(LIM)}$ level as set by $R_{(ILIM)}$
	Power dissipation increases as $V_{(IN)}$ - $V_{(OUT)}$ grows
	Device turns off when $T_J > T_{(TSD)}$
	'L' Version remains off
	'A' Version will attempt restart $t_{TSD(dly)}$ ms after $T_J < [T_{(TSD)}$ -20°C]
Short-Circuit Response	Fast shut off when $I_{(LOAD)} > I_{(FASTRIP)}$
	Quick restart and current limited to I_{LIMIT}, follows standard startup cycle

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10 Applications and Implementation

10.1 Application Information

The TPS25921x is a smart eFuse. It is typically used for Hot-Swap and Power rail protection applications. It operates from 4.5 V to 18 V with programmable current limit, overvoltage and undervoltage protection. The device aids in controlling the in-rush current and provides precise current limiting during overload conditions for systems such as White Goods, Set-Top-Box, DTVs, Gaming Consoles, SSDs/HDDs and Smart Meters. The device also provides robust protection for multiple faults on the sub-system rail.

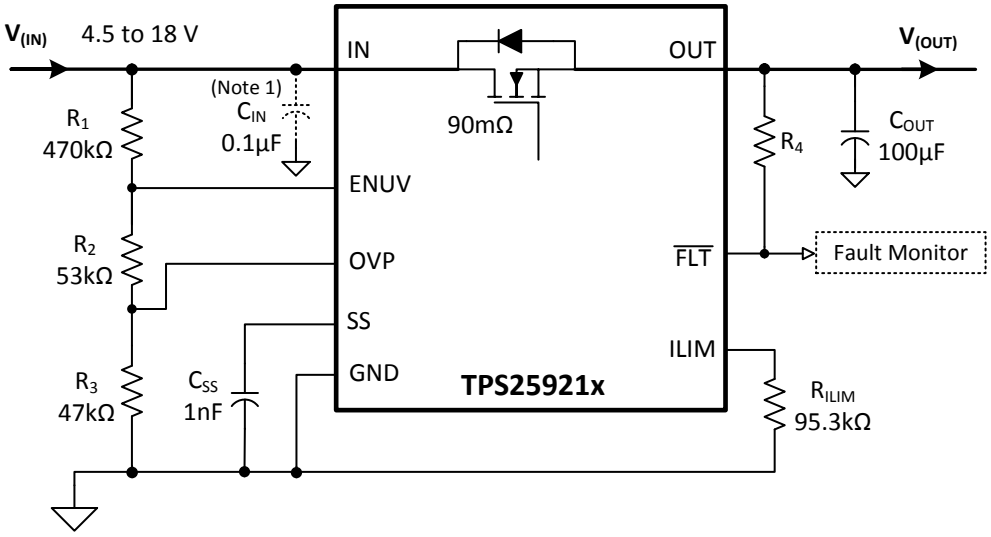
The following design procedure can be used to select component values for the device.

Alternatively, the WEBENCH® software may be used to generate a complete design. The WEBENCH® software uses an iterative design procedure and accesses a comprehensive database of components when generating a design. Additionally, a spreadsheet design tool *TPS25921 Design Calculator* is available on web folder.

This section presents a simplified discussion of the design process.

10.2 Typical Application

10.2.1 Precision Current Limiting and Protection for White Goods



(1) C_{IN}: Optional and only for noise suppression.

Figure 30. Typical Application Schematics: eFuse for White Goods

10.2.1.1 Design Requirements

Table 2. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range, $V_{(IN)}$	12 V
Undervoltage lockout set point, $V_{(UV)}$	8 V
Overvoltage protection set point , $V_{(OV)}$	17 V
Load at Start-Up , $R_{L(SU)}$	24 Ω
Current limit, I_{LIMIT}	1 A
Load capacitance , $C_{(OUT)}$	100 µF
Maximum ambient temperatures , T_A	85°C

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10.2.1.2 Detailed Design Procedure

The following design procedure can be used to select component values for the TPS25921A and TPS25921L.

10.2.1.2.1 Step by Step Design Procedure

To begin the design process a few parameters must be decided upon. The designer needs to know the following:

- Normal input operation voltage
- Maximum output capacitance
- Maximum current Limit
- Load during start-up
- Maximum ambient temperature of operation

This design procedure below seeks to control the junction temperature of device under both static and transient conditions by proper selection of output ramp-up time and associated support components. The designer can adjust this procedure to fit the application and design criteria.

10.2.1.2.2 Programming the Current-Limit Threshold: $R_{(ILIM)}$ Selection

The $R_{(ILIM)}$ resistor at the ILIM pin sets the over load current limit, this can be set using Equation 5.

$$R_{(ILIM)} = \frac{1 + 0.018}{10.73 \times 10^{-3}} = 94.8\ k\Omega \quad (8)$$

Choose closest standard value: 95.3 kΩ, 1% standard value resistor.

10.2.1.2.3 Undervoltage Lockout and Overvoltage Set Point

The undervoltage lockout (UVLO) and overvoltage trip point are adjusted using the external voltage divider network of R_1, R_2 and R_3 as connected between IN, ENUV, OVP and GND pins of the device. The values required for setting the undervoltage and overvoltage are calculated solving Equation 9 and Equation 10.

$$V_{(OVPR)} = \frac{R_3}{R_1 + R_2 + R_3} \times V_{(OV)} \quad (9)$$

$$V_{(ENR)} = \frac{R_2 + R_3}{R_1 + R_2 + R_3} \times V_{(UV)} \quad (10)$$

For minimizing the input current drawn from the power supply $\{I_{(R123)} = V_{(IN)}/(R_1 + R_2 + R_3)\}$, it is recommended to use higher values of resistance for R_1, R_2 and R_3.

However, leakage currents due to external active components connected to the resistor string can add error to these calculations. So, the resistor string current, $I_{(R123)}$ must be chosen to be 20x greater than the leakage current expected.

From the device electrical specifications, $V_{(OVPR)}$ = 1.40 V and $V_{(ENR)}$ = 1.40 V. For design requirements, $V_{(OV)}$ is 17 V and $V_{(UV)}$ is 8 V. To solve the equation, first choose the value of R_3 = 47 kΩ and use Equation 9 to solve for $(R_1 + R_2)$ = 523.71 kΩ. Use Equation 10 and value of $(R_1 + R_2)$ to solve for R_2 = 52.88 kΩ and finally R_1= 470.83 kΩ.

Using the closest standard 1% resistor values gives R_1 = 470 kΩ, R_2 = 53 kΩ, and R_3 = 47 kΩ.

The power failure threshold is detected on the falling edge of supply. This threshold voltage is 4% lower than the rising threshold, $V_{(UV)}$. This is calculated using Equation 11.

$$V_{(PFAIL)} = 0.96 \times V_{(UV)} \quad (11)$$

Power fail threshold set is : 7.68 V

10.2.1.2.4 Setting Output Voltage Ramp time (t_{SS})

For a successful design, the junction temperature of device should be kept below the absolute-maximum rating during both dynamic (start-up) and steady state conditions. Dynamic power stresses often are an order of magnitude greater than the static stresses, so it is important to determine the right start-up time and in-rush current limit required with system capacitance to avoid thermal shutdown during start-up with and without load.

The ramp-up capacitor $C_{(SS)}$ needed is calculated considering the two possible cases:

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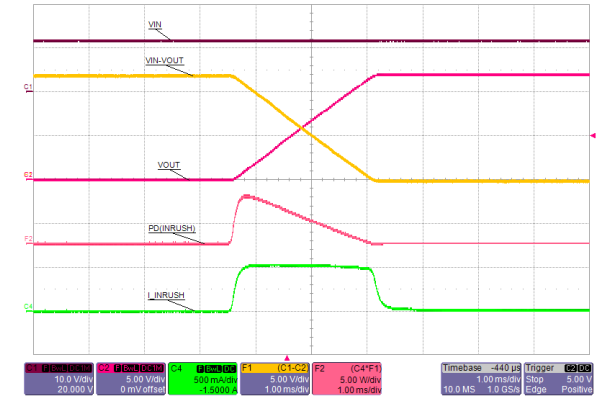
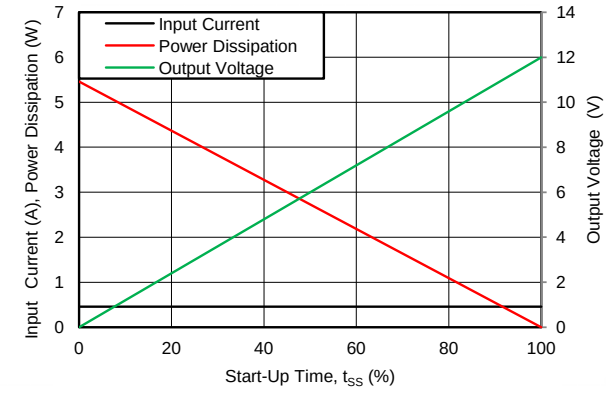
10.2.1.2.4.1 Case1: Start-up Without Load: Only Output Capacitance $C_{(OUT)}$ Draws Current During Start-up

During start-up, as the output capacitor charges, the voltage difference across the internal FET decreases, and the power dissipated decreases as well. Typical ramp-up of output voltage $V_{(OUT)}$ with inrush current limit of 0.5A and power dissipated in the device during start-up is shown in Figure 31. The average power dissipated in the device during start-up is equal to area of triangular plot (red curve in Figure 32) averaged over t_{SS}.



$V_{(IN)}$ = 12 V $C_{(SS)}$ = 1 nF $C_{(OUT)}$=100 µF

Figure 31. Start-up Without Load



$V_{(IN)}$ = 12 V $C_{(SS)}$ = 1 nF $C_{(OUT)}$=100 µF

Figure 32. $P_{D(INRUSH)}$ Due to Inrush Current

For TPS25921 device, the inrush current is determined as,

$$I = C \times \frac{dV}{dT} \Rightarrow I_{(INRUSH)} = C_{(OUT)} \times \frac{V_{(IN)}}{t_{SS}} \quad (12)$$

Power dissipation during start-up is:

$$P_{D(INRUSH)} = 0.5 \times V_{(IN)} \times I_{(INRUSH)} \quad (13)$$

Equation 13 assumes that load does not draw any current until the output voltage has reached its final value.

10.2.1.2.4.2 Case 2: Start-up With Load: Output Capacitance $C_{(OUT)}$ and Load Draws Current During Start-up

When load draws current during the turn-on sequence, there will be additional power dissipated. Considering a resistive load $R_{L(SU)}$ during start-up, load current ramps up proportionally with increase in output voltage during t_{SS} time. Typical ramp-up of output voltage, load current and power dissipation in the device is shown in Figure 33 and power dissipation with respect to time is plotted in Figure 34. The additional power dissipation during start-up phase is calculated as follows.

$$(V_I - V_O)(t) = V_{(IN)} \times \left(1 - \frac{t}{t_{SS}}\right) \quad (14)$$

$$I_L(t) = \left(\frac{V_{(IN)}}{R_{L(SU)}}\right) \times \frac{t}{t_{SS}} \quad (15)$$

Where $R_{L(SU)}$ is the load resistance present during start-up. Average energy loss in the internal FET during charging time due to resistive load is given by:

$$W_t = \int_0^{tss} V_{(IN)} \times \left(1 - \frac{t}{t_{SS}}\right) \times \left(\frac{V_{(IN)}}{R_{L(SU)}} \times \frac{t}{t_{SS}}\right) dt \quad (16)$$

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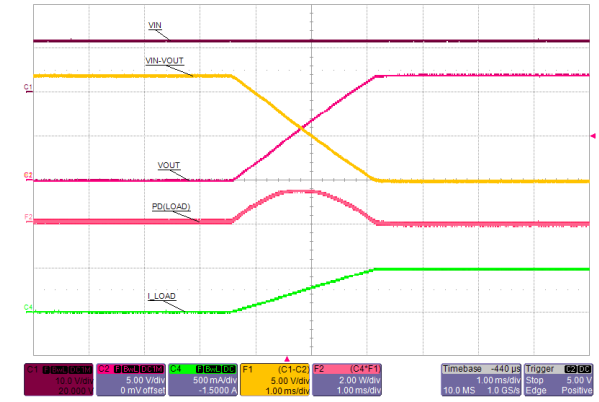
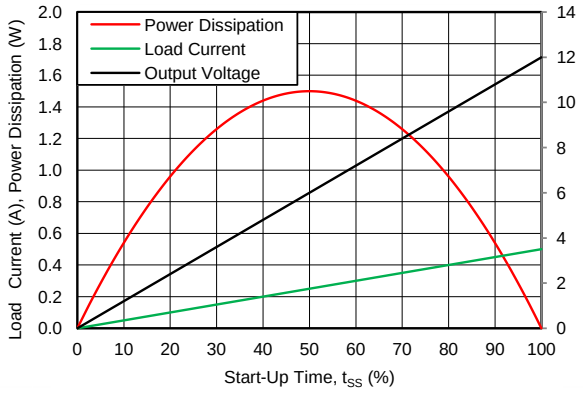


$V_{(IN)}$ = 12 V $C_{(SS)}$ = 1 nF , $C_{(OUT)}$=100 µF $R_{L(SU)}$ = 24 Ω

Figure 33. Start-up With Load



$V_{(IN)}$ = 12 V $C_{(SS)}$ = 1 nF $R_{L(SU)}$ = 24 Ω

Figure 34. $P_{D(LOAD)}$ in Device during Start-up with Load

On solving Equation 16 the average power loss in the internal FET due to load is:

$$P_{D(LOAD)} = \left(\frac{1}{6}\right) \times \frac{V^2_{(IN)}}{R_{L(SU)}} \quad (17)$$

Total power dissipated in the device during startup is:

$$P_{D(STARTUP)} = P_{D(INRUSH)} + P_{D(LOAD)} \quad (18)$$

Total current during startup is given by:

$$I_{(STARTUP)} = I_{(INRUSH)} + I_L(t) \quad (19)$$

If $I_{(STARTUP)} > I_{LIMIT}$, the device limits the current to I_{LIMIT} and the current limited charging time is determined by:

$$t_{SS(current\text{-}limited)} = C_{(OUT)} \times R_{L(SU)} \times \left[\frac{I_{(LIMIT)}}{I_{(INRUSH)}} - 1 + LN\left(\frac{I_{(INRUSH)}}{I_{(LIMIT)} - \frac{V_{(IN)}}{R_{L(SU)}}}\right)\right] \quad (20)$$

The power dissipation, with and without load, for selected start-up time should not exceed the shutdown limits as shown in Figure 35.

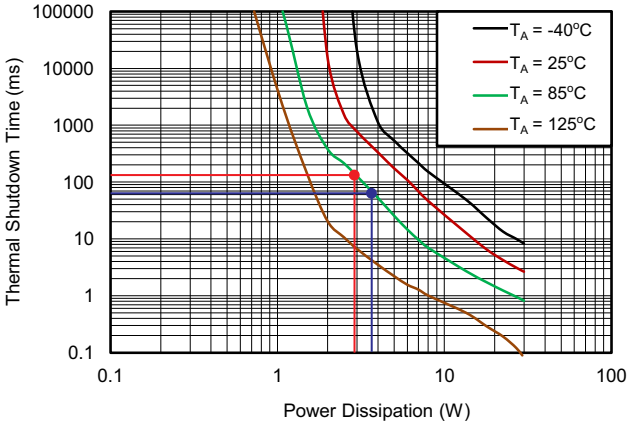


Figure 35. Thermal Shutdown Limit Plot

For the design example under discussion,

Select ramp-up capacitor $C_{(SS)}$ = 1nF, using Equation 2.

$$t_{SS} = 20.6 \times 10^4 \times 12 \times (1 + 0.07) = 2.64 \text{ ms} \quad (21)$$

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The inrush current drawn by the load capacitance ($C_{(OUT)}$) during ramp-up using Equation 3.

$$I_{(INRUSH)} = \left(100 \times 10^{-6}\right) \times \left(\frac{12}{2.64 \times 10^{-3}}\right) = 0.454 \text{ A} \quad (22)$$

The inrush Power dissipation is calculated, using Equation 13.

$$P_{D(INRUSH)} = 0.5 \times 12 \times 0.454 = 2.72 \text{ W} \quad (23)$$

For 2.72 W of power loss, the thermal shut down time of the device should not be less than the ramp-up time t_{SS} to avoid the false trip at maximum operating temperature. From thermal shutdown limit graph Figure 35 at T_A = 85°C, for 2.72 W of power the shutdown time is ~170 ms. So it is safe to use 2.64 ms as start-up time without any load on output.

Considering the start-up with load 24 Ω, the additional power dissipation, when load is present during start up is calculated, using Equation 17.

$$P_{D(LOAD)} = \left(\frac{1}{6}\right) \times \left(\frac{12 \times 12}{24}\right) = 1 \text{ W} \quad (24)$$

The total device power dissipation during start up is:

$$P_{D(STARTUP)} = 2.72 + 1 = 3.72 \text{ W} \quad (25)$$

From thermal shutdown limit graph at T_A = 85°C, the thermal shutdown time for 3.72 W is close to 60 ms. It is safe to have 30% margin to allow for variation of system parameters such as load, component tolerance, and input voltage. So it is well within acceptable limits to use the 1 nF capacitor with start-up load of 24 Ω.

If there is a need to decrease the power loss during start-up, it can be done with increase of $C_{(SS)}$ capacitor.

To illustrate, choose $C_{(SS)}$ = 4.7 nF as an option and recalculate:

$$t_{SS} = 20.6 \times 10^4 \times 12 \times (4.7 + 0.07) = 11.8 \text{ ms} \quad (26)$$

$$I_{(INRUSH)} = \left(100 \times 10^{-6}\right) \times \left(\frac{12}{11.8 \times 10^{-3}}\right) = 0.102 \text{ A} \quad (27)$$

$$P_{D(INRUSH)} = 0.5 \times 12 \times 0.102 = 0.61 \text{ W} \quad (28)$$

$$P_{D(LOAD)} = \left(\frac{1}{6}\right) \times \left(\frac{12 \times 12}{24}\right) = 1 \text{ W} \quad (29)$$

$$P_{D(STARTUP)} = 0.61 + 1 = 1.61 \text{ W} \quad (30)$$

From thermal shutdown limit graph at T_A = 85°C, the shutdown time for 1.61 W power dissipation is ~1000 ms, which increases the margins further for shutdown time and ensures successful operation during start up and steady state conditions.

The spreadsheet tool available on the web can be used for iterative calculations.

10.2.1.2.5 Support Component Selections - R_4 and C_{IN}

Reference to application schematics, R_4 is required only if $\overline{FLT}$ is used; The resistor serves as pull-up for the open-drain output driver. The current sunk by this pin should not exceed 100 mA (refer to the *Absolute Maximum Ratings* table). C_{IN} is a bypass capacitor to help control transient voltages, unit emissions, and local supply noise. Where acceptable, a value in the range of 0.001 µF to 0.1 µF is recommended for $C_{(IN)}$.

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10.2.1.3 Application Curves

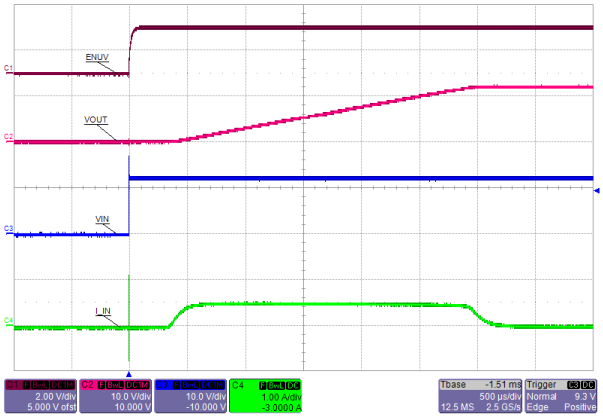

Figure 36. Hot-Plug Start-Up: Output Ramp Without Load on Output

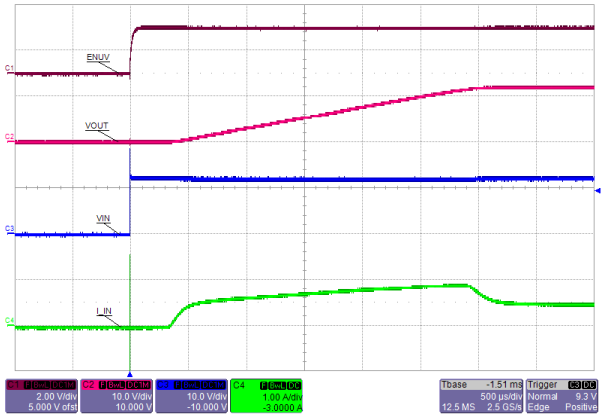

Figure 37. Hot-Plug Start-Up: Output Ramp With 24 Ω Load at Start Up

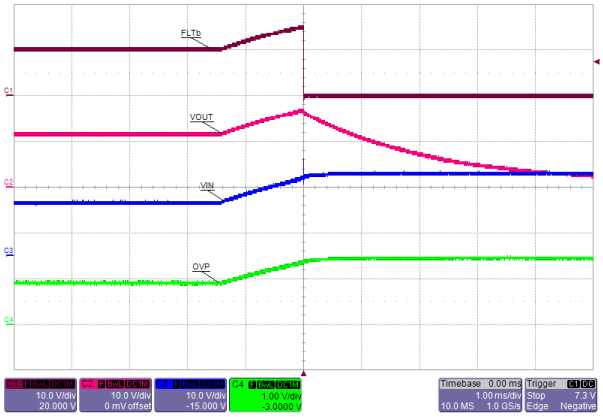

Figure 38. Overvoltage Shutdown

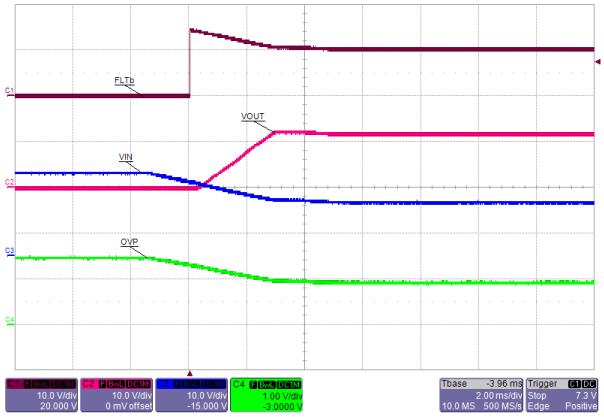

Figure 39. Overvoltage Recovery

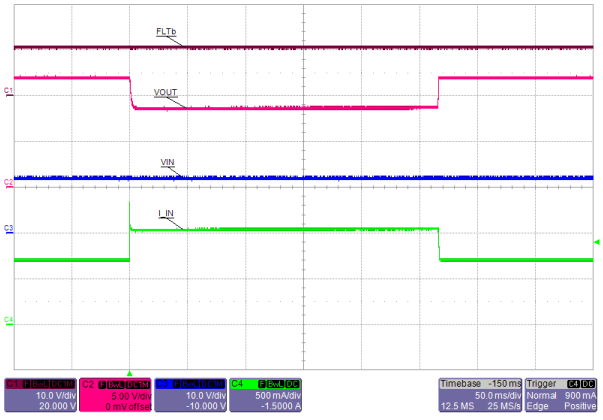

Figure 40. Over Load: Step Change in Load from 19 Ω to 9 Ω Back

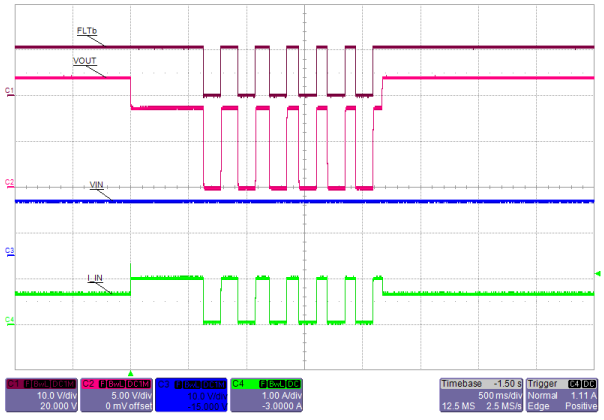

Figure 41. Overload Condition: Auto Retry and Recovery - TPS25921A

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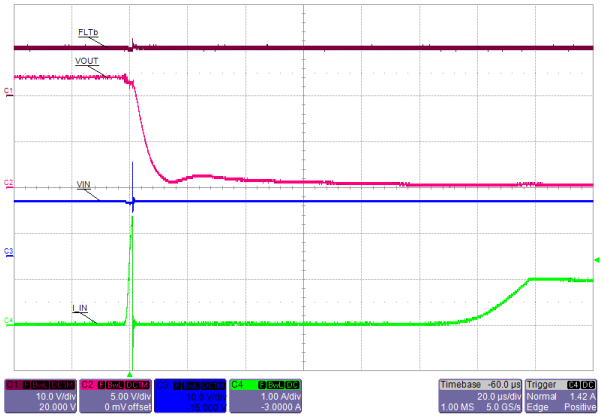

Figure 42. Hot Short: Fast Trip and Current Regulation

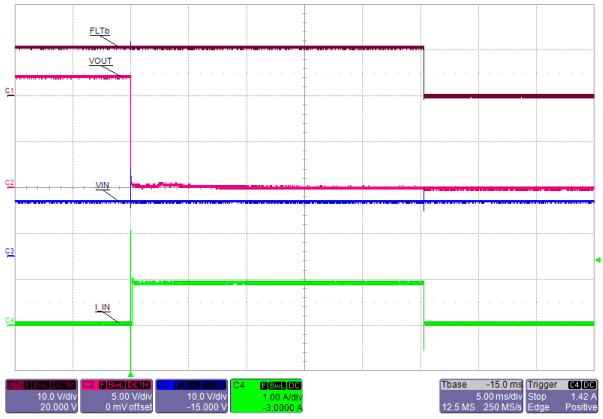

Figure 43. Hot Short: Latched - TPS25921L

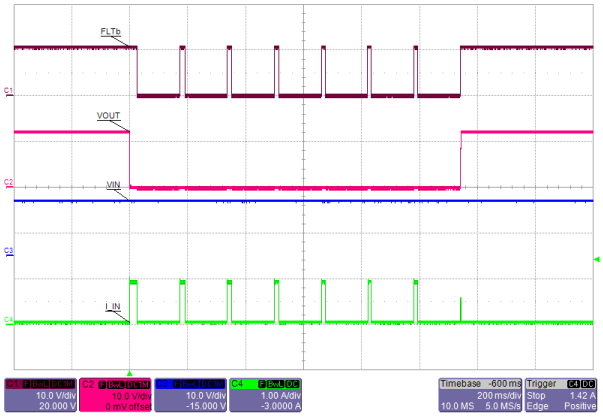

Figure 44. Hot Short: Auto-Retry and Recovery from Short Circuit - TPS25921A

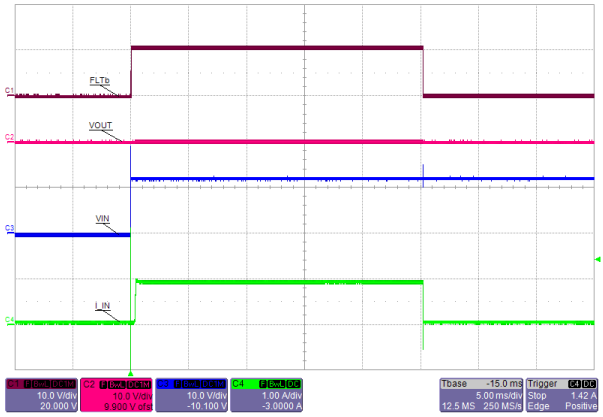

Figure 45. Hot Plug-in with Short on Output: Latched - TPS25921L

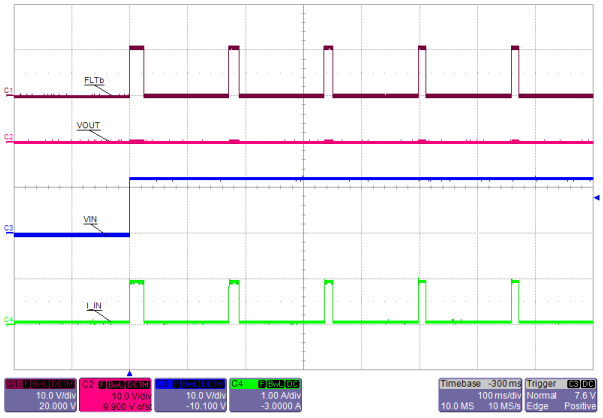

Figure 46. Hot Plug-in with Short on Output: Auto-Retry - TPS25921A

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11 System Examples

The TPS25921 provides a simple solution for current limiting, inrush current control and supervision of power rails for wide range of applications operating at 4.5 V to 18 V and delivering up to 1.5 A.

11.1 Protection and Current Limiting for Primary-Side Regulated Power Supplies

Primary side regulated power supplies and adapters are dominant today in many of the applications such as Smart-phones, Portable hand-held devices, White Goods, Set-Top-Box and Gaming consoles. These supplies provide efficient, low cost and low component count solutions for power needs ranging from 5W to 30W. But, these come with drawbacks of

- No secondary side protection for immediate termination of critical faults such as short circuit and over voltage
- Do not provide precise current limiting for overload transients
- Have poor output voltage regulation for sudden change in AC input voltages - triggering output overvoltage condition

Many of the above applications require precise output current limiting and secondary side protection, driving the need for current sensing in the secondary side. This needs additional circuit implementation using precision operational amplifiers. This increases the complexity of the solution and also results in sensing losses The TPS25921 with its integrated low-ohmic N-channel FET provides a simple and efficient solution. Figure 47 shows the typical implementation using TPS25921.

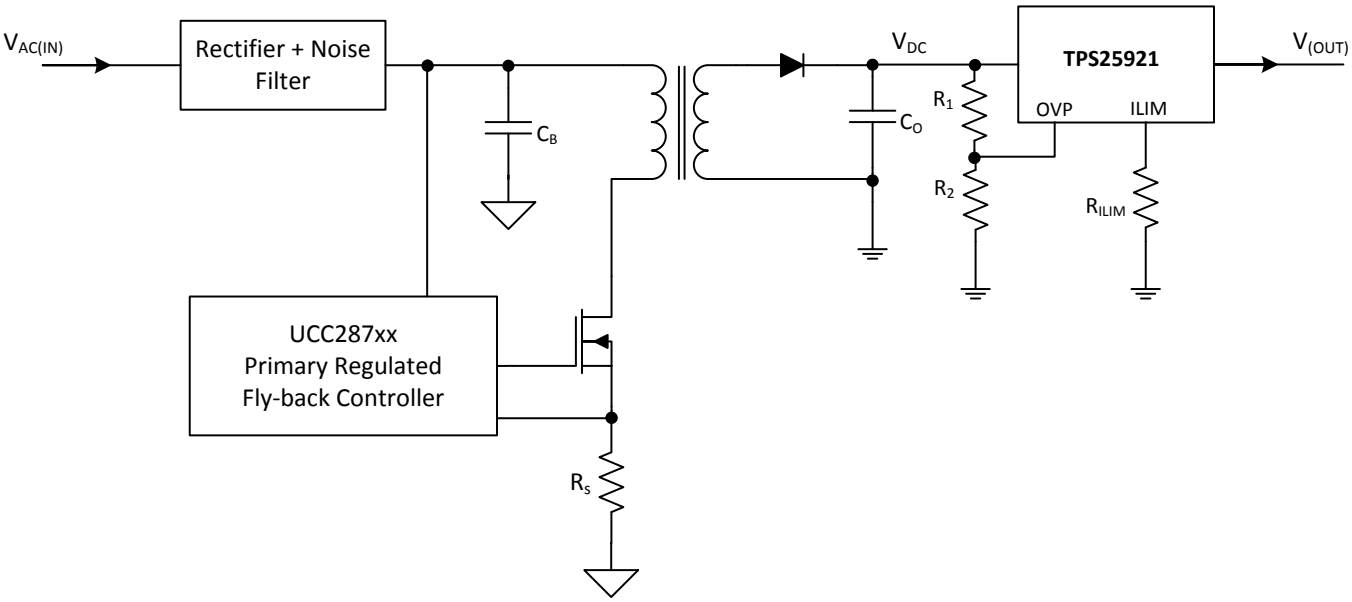

Figure 47. Current Limiting and Protection for AC-DC Power Supplies

During short circuit conditions, the internal fast comparator of TPS25921 turns OFF the internal FET in less than 3 µs (typical) as soon as current exceeds $I_{(FASTRIP)}$, set by the current limit $R_{(ILIM)}$ resistor. The OVP comparator with 3% precision helps in quick isolation of the load from the input when inputs exceeds the set $V_{(OVPR)}$

Figure 42 and Figure 38 shows short circuit and overvoltage response waveforms of implementation using TPS25921. In addition to above, the TPS25921 provides inrush current limit when output is hot-plugged into any of the system loads.

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11.2 Precision Current Limiting in Intrinsic Safety Applications

Intrinsic safety (IS) is becoming prominent need for safe operation of electrical and electronic equipment in hazardous areas. Intrinsic safety requires that equipment is designed such that the total amount of energy available in the apparatus is simply not enough to ignite an explosive atmosphere. The energy can be electrical, in the form of a spark, or thermal, in the form of a hot surface.

This calls for precise current limiting and precision shutdown of the circuit for over voltage conditions ensuring that set voltage and current limits are not exceeded for wide operating temperature range and variable environmental conditions. Applications such as Gas Analyzers, Medical equipment (such as electrocardiographs), Portal Industrial Equipment, Cabled Power distribution systems and hand-held motor operated tools need to meet these critical safety standards.

The TPS25921 device can be used as simple protection solution for each of the internal rails. Figure 48 shows the typical implementation using TPS25921.

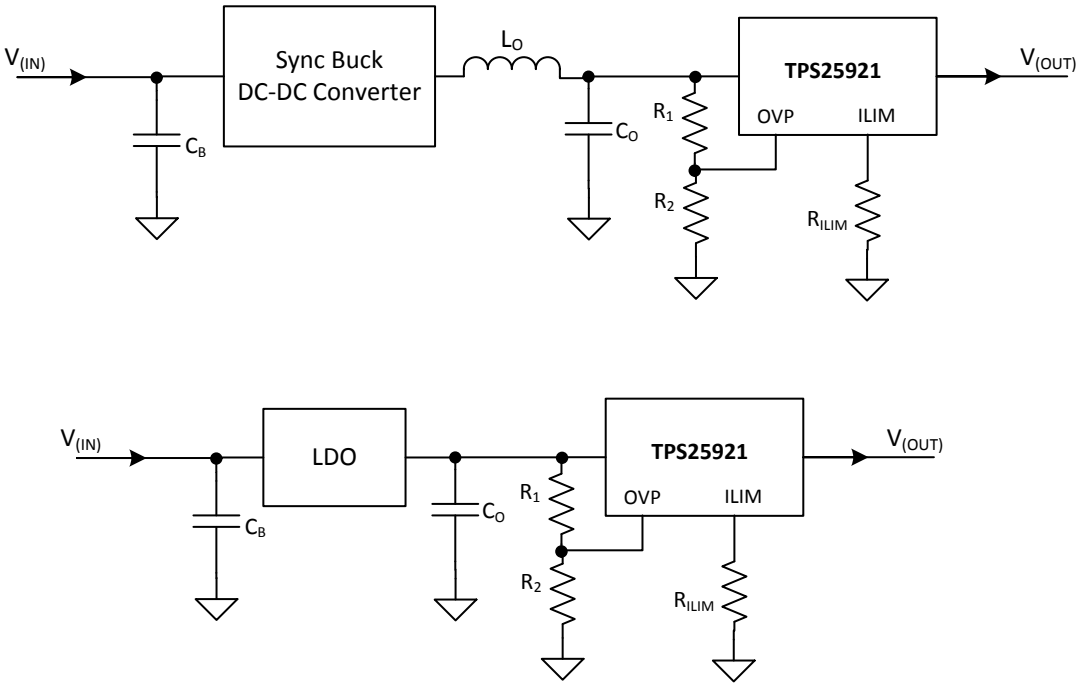

Figure 48. Precision current Limit and Protection of Internal Rails

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11.3 Smart Load Switch

A smart load switch is a series FET used for switching of the load (resistive or inductive). It also provides protection during fault conditions. Typical discrete implementation is shown in Figure 49. Discrete solutions have higher component count and require complex circuitry to implement each of the protection fault needs.

TPS25921 can be used as a smart power switch for applications ranging from 4.5 V to 18 V. TPS25921 provides programmable soft start, programmable current limits, over-temperature protection, a fault flag, and under-voltage lockout.

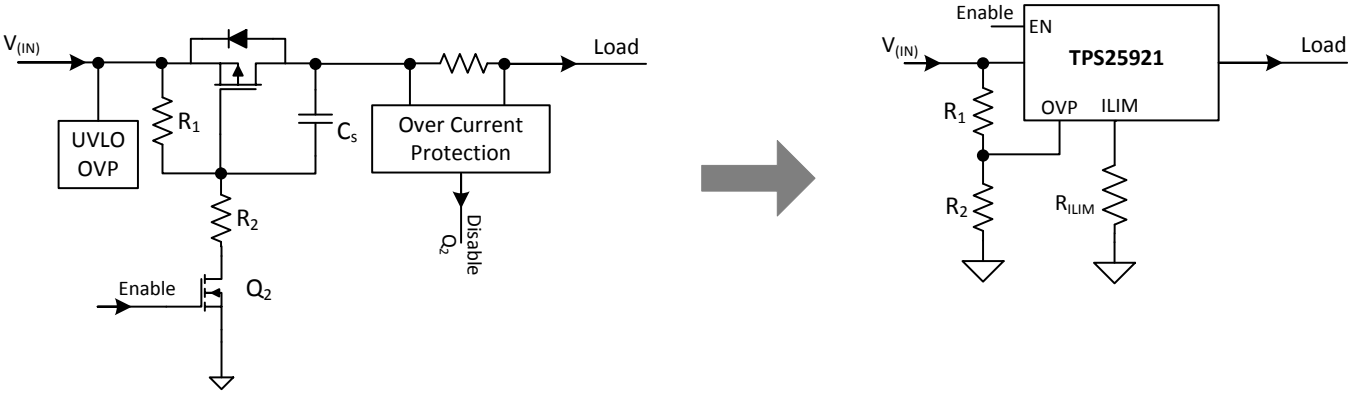

Figure 49. Smart Load Switch Implementation

Figure 49 shows typical implementation and usage as load switch. This configuration can be used for driving a solenoid and FAN control. It is recommended to use a freewheeling diode across the load when load is highly inductive.

Figure 50 shows load switching waveforms using TPS25921 for 12 V Bus

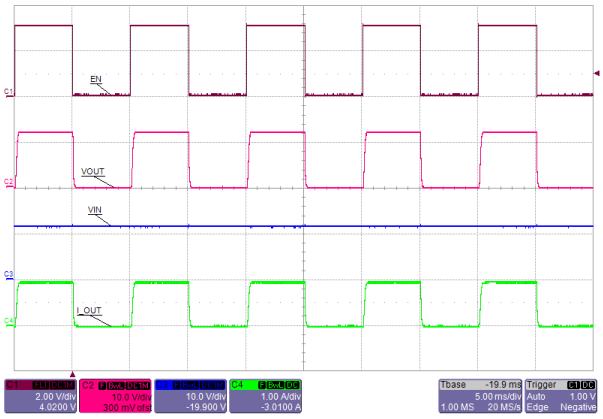

Figure 50. Smart Load Switch (100 Hz Operation)

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12 Power Supply Recommendations

The device is designed for supply voltage range of 4.5 V ≤ V_{IN} ≤ 18 V. If the input supply is located more than a few inches from the device an input ceramic bypass capacitor higher than 0.1 µF is recommended. Power supply should be rated higher than the current limit set to avoid voltage droops during over current and short-circuit conditions.

12.1 Transient Protection

In case of short circuit and over load current limit, when the device interrupts current flow, input inductance generates a positive voltage spike on the input and output inductance generates a negative voltage spike on the output. The peak amplitude of voltage spikes (transients) is dependent on value of inductance in series to the input or output of the device. Such transients can exceed the *Absolute Maximum Ratings* of the device if steps are not taken to address the issue.

Typical methods for addressing transients include

- Minimizing lead length and inductance into and out of the device
- Using large PCB GND plane
- Schottky diode across the output to absorb negative spikes
- A low value ceramic capacitor ($C_{(IN)}$ = 0.001 µF to 0.1 µF) to absorb the energy and dampen the transients. The approximate value of input capacitance can be estimated with Equation 31.

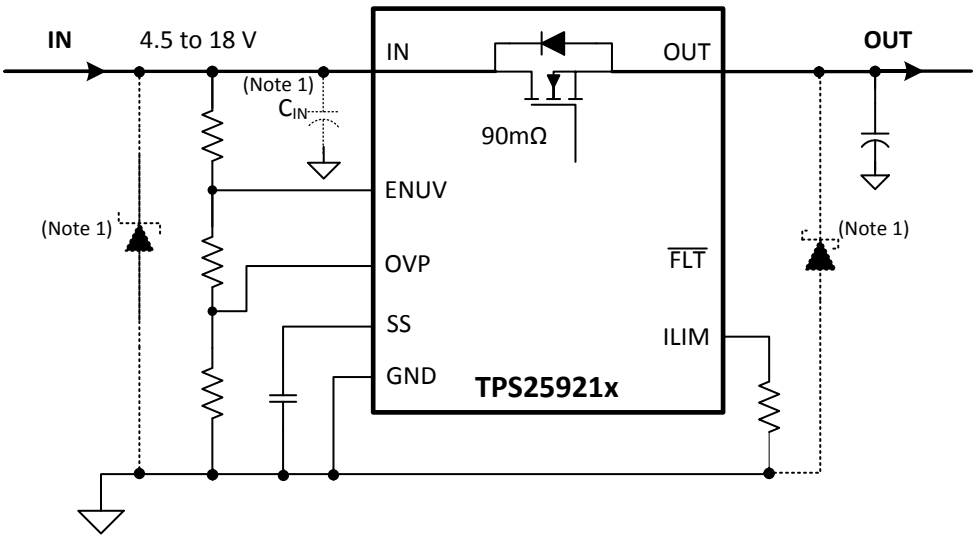
$$V_{SPIKE(Absolute)} = V_{(IN)} \times I_{(LOAD)} \times \sqrt{\frac{L_{(IN)}}{C_{(IN)}}} \quad (31)$$

Where:

- $V_{(IN)}$ is the nominal supply voltage
- $I_{(LOAD)}$ is the load current,
- $L_{(IN)}$ equals the effective inductance seen looking into the source
- $C_{(IN)}$ is the capacitance present at the input

Some applications may require the addition of a Transient Voltage Suppressor (TVS) to prevent transients from exceeding the *Absolute Maximum Ratings* of the device.

The circuit implementation with optional protection components (a ceramic capacitor, TVS and schottky diode) is shown in Figure 51.



(1) Optional components needed for suppression of transients

Figure 51. Circuit Implementation With Optional Protection Components

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12.2 Output Short-Circuit Measurements

It is difficult to obtain repeatable and similar short-circuit testing results. Source bypassing, input leads, circuit layout and component selection, output shorting method, relative location of the short, and instrumentation all contribute to variation in results. The actual short itself exhibits a certain degree of randomness as it microscopically bounces and arcs. Care in configuration and methods must be used to obtain realistic results. Do not expect to see waveforms exactly like those in the data sheet; every setup differs.

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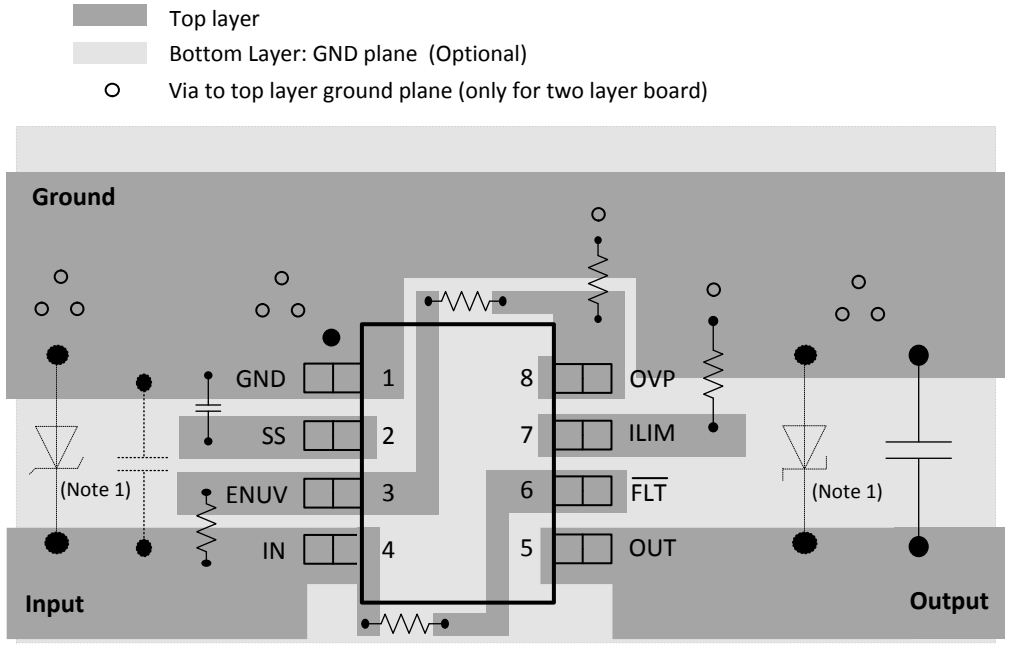
13 Layout

13.1 Layout Guidelines

- For all applications, a 0.01-uF or greater ceramic decoupling capacitor is recommended between IN terminal and GND. For hot-plug applications, where input power path inductance is negligible, this capacitor can be eliminated/minimized.
- The optimum placement of decoupling capacitor is closest to the IN and GND terminals of the device. Care must be taken to minimize the loop area formed by the bypass-capacitor connection, the IN terminal, and the GND terminal of the IC. See Figure 52 for a PCB layout example.
- High current carrying power path connections should be as short as possible and should be sized to carry at least twice the full-load current.
- The GND terminal must be tied to the PCB ground plane at the terminal of the IC. The PCB ground should be a copper plane or island on the board.
- Locate all TPS25921x support components: $R_{(ILIM)}$, C_{SS}, and resistors for $\overline{FLT}$, ENUV and OVP, close to their connection pin. Connect the other end of the component to the GND pin of the device with shortest trace length.
- The trace routing for the R_{ILIM} and C_{SS} components to the device should be as short as possible to reduce parasitic effects on the current limit and soft start timing. These traces should not have any coupling to switching signals on the board.
- OVP and ENUV signal traces should be routed with sufficient spacing from $\overline{FLT}$ signal trace, to avoid spurious coupling of $\overline{FLT}$ switching, during fault conditions.
- Protection devices such as TVS, snubbers, capacitors, or diodes should be placed physically close to the device they are intended to protect, and routed with short traces to reduce inductance. For example, a protection Schottky diode is recommended to address negative transients due to switching of inductive loads, and it should be physically close to the OUT pins.
- Obtaining acceptable performance with alternate layout schemes is possible; however this layout has been shown to produce good results and is intended as a guideline.

13.2 Layout Example



(1) Optional: Needed only to suppress the transients caused by inductive load switching.

Figure 52. Board Layout

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14 器件和文档支持

14.1 相关链接

以下表格列出了快速访问链接。 范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

Table 3. 相关链接

部件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
TPS25921A	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
TPS25921L	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

14.2 Trademarks

14.3 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

14.4 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、首字母缩略词和定义。

15 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS25921AD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	25921A	Samples
TPS25921ADR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	25921A	Samples
TPS25921LD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	25921L	Samples
TPS25921LDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	25921L	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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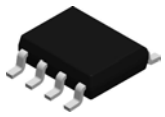
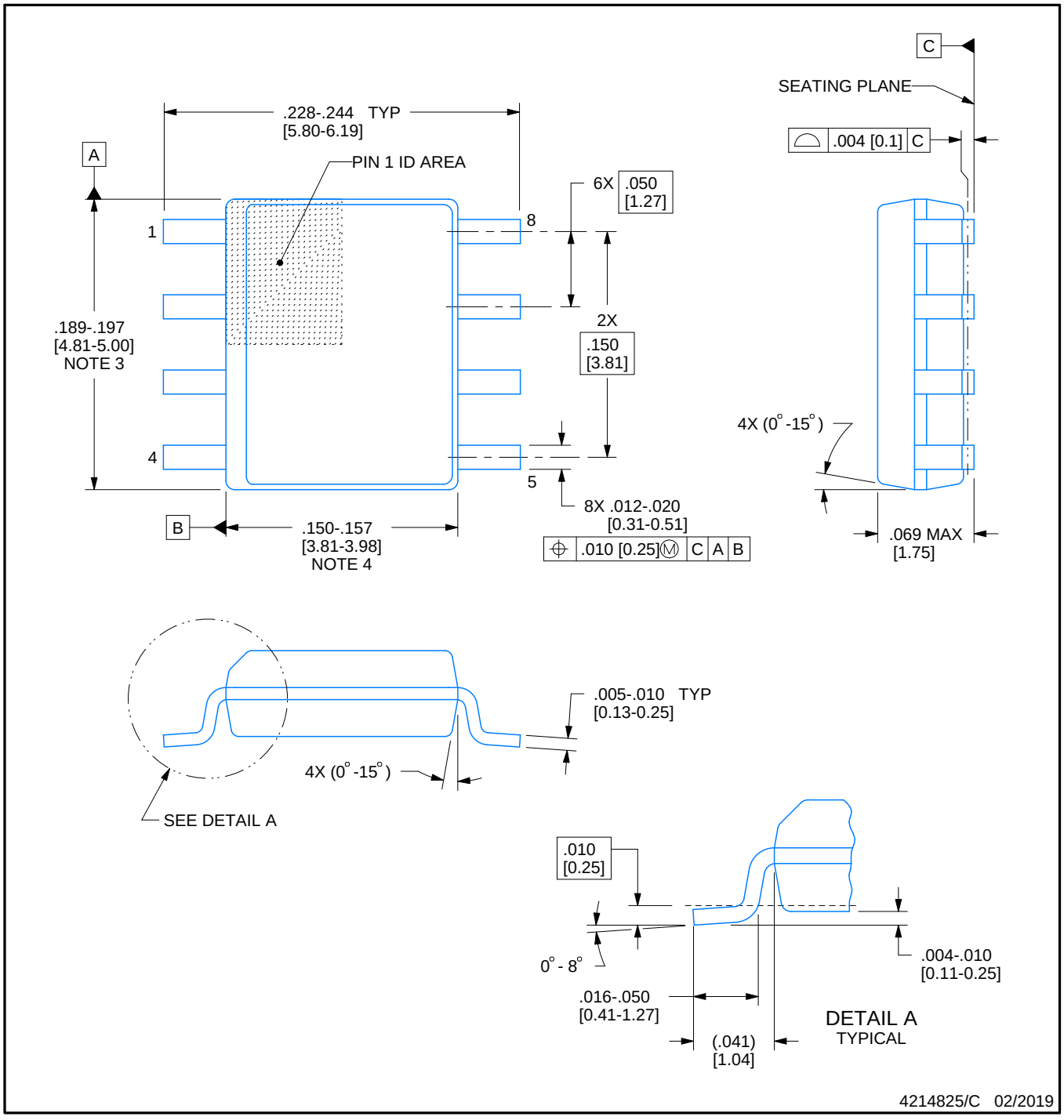


PACKAGE OUTLINE

D0008A

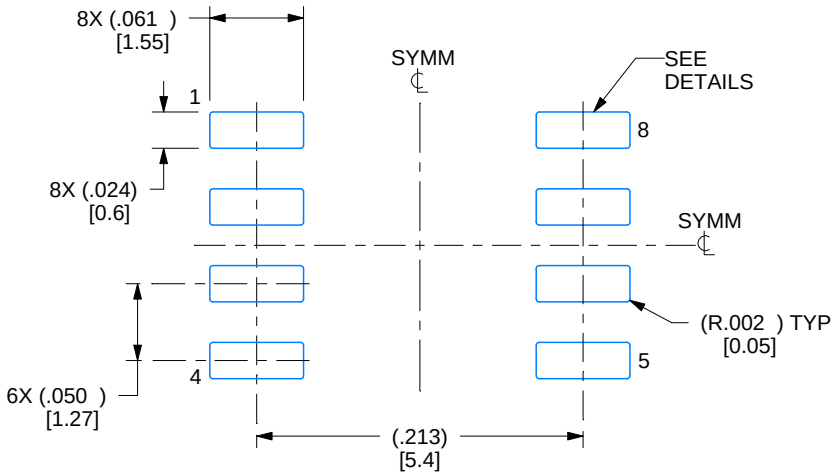
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

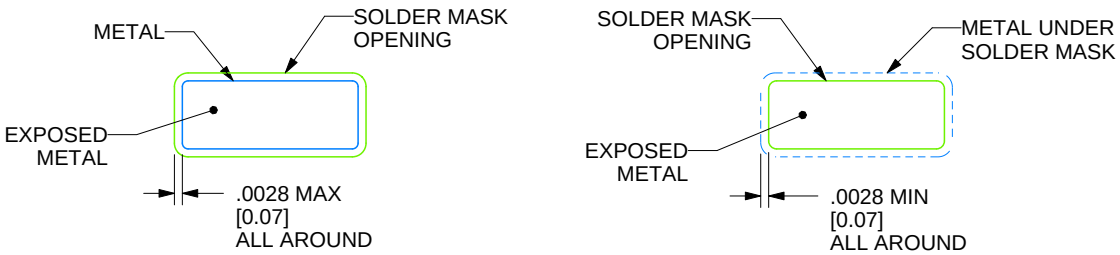


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

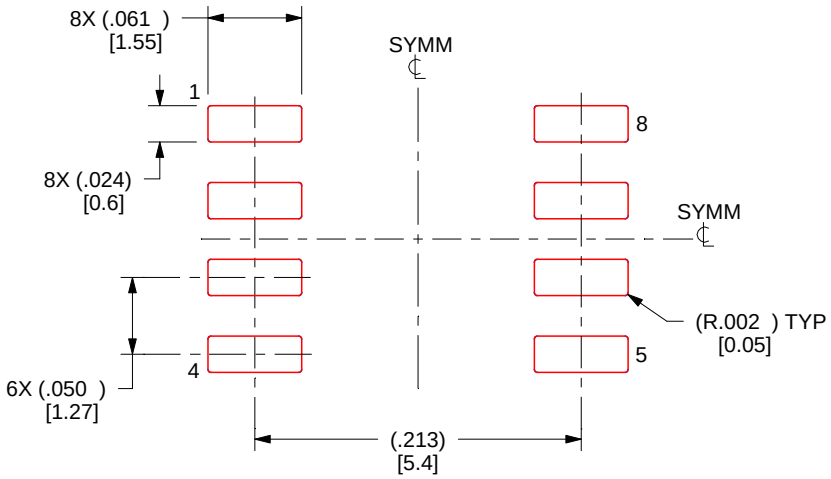
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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